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April 1st, 2010
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (<http://www.renesas.com>)

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MOS INTEGRATED CIRCUIT

μPD703034A, 703034AY, 703035A, 703035AY, 70F3035A, 70F3035AY

V850/SB2™

32-BIT SINGLE-CHIP MICROCONTROLLERS

DESCRIPTION

The μPD703034A, 703034AY, 703035A, 703035AY, 70F3035A, and 70F3035AY (V850/SB2) are 32-bit single-chip microcontrollers of the V850 Family™ for AV equipment. 32-bit CPU, ROM, RAM, timer/counters, serial interfaces, A/D converter, DMA controller, and so on are integrated on a single chip.

The μPD70F3035A and 70F3035AY have flash memory in place of the internal mask ROM of the μPD703035A and 703035AY. Because flash memory allows the program to be written and erased electrically with the device mounted on the board, these products are ideal for the evaluation stages of system development, small-scale production, and rapid development of new products.

The μPD703037A, 703037AY, 70F3037A, 70F3037AY, products with a different ROM/RAM size are also available.

Detailed function descriptions are provided in the following user's manuals. Be sure to read them before designing.

V850/SB1™, V850/SB2 User's Manual Hardware: U13850E
V850 Family User's Manual Architecture: U10243E

FEATURES

- Number of instructions: 74
- Minimum instruction execution time: 76.9 ns (@ internal 13 MHz operation)
- General-purpose registers: 32 bits × 32 registers
- Instruction set: Signed multiplication, saturation operations, 32-bit shift instructions, bit manipulation instructions, load/store instructions
- Memory space: 16 MB linear address space
- Internal memory ROM: 128 KB (μPD703034A, 703034AY: mask ROM)
 256 KB (μPD703035A, 703035AY: mask ROM)
 256 KB (μPD70F3035A, 70F3035AY: flash memory)
- RAM: 12 KB (μPD703034A, 703034AY)
 16 KB (μPD703035A, 703035AY, 70F3035A, 70F3035AY)
- Interrupt/exception: μPD703034A, 703035A, 70F3035A (external: 8, internal: 33 sources, exception: 1 source)
 μPD703034AY, 703035AY, 70F3035AY (external: 8, internal: 34 sources, exception: 1 source)
- I/O lines Total: 83
- Timer/counters: 16-bit timer (2 channels: TM0, TM1)
 8-bit timer (6 channels: TM2 to TM7)
- Watch timer: 1 channel
- Watchdog timer: 1 channel
- IEBus™ controller: 1 channel

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

- Serial interface
 - Asynchronous serial interface (UART0, UART1)
 - Clocked serial interface (CSI0 to CSI3)
 - 3-wire variable length serial interface (CSI4)
 - I²C bus interface (I²C0, I²C1) (μPD703034AY, 703035AY, 70F3035AY only)
- 10-bit resolution A/D converter: 12 channels
- DMA controller: 6 channels
- Real-time output port: 8 bits × 1 channel or 4 bits × 2 channels
- ROM correction: 4 places can be corrected
- Power-saving function: HALT/IDLE/STOP modes
- Packages: 100-pin plastic LQFP (fine pitch) (14 × 14)
100-pin plastic QFP (14 × 20)
- μPD70F3035A, 70F3035AY
 - Can be replaced with μPD703035A and 703035AY (internal mask ROM) in mass production

APPLICATIONS

- AV equipment (audio, car audio, VCR, TV, etc.)

ORDERING INFORMATION

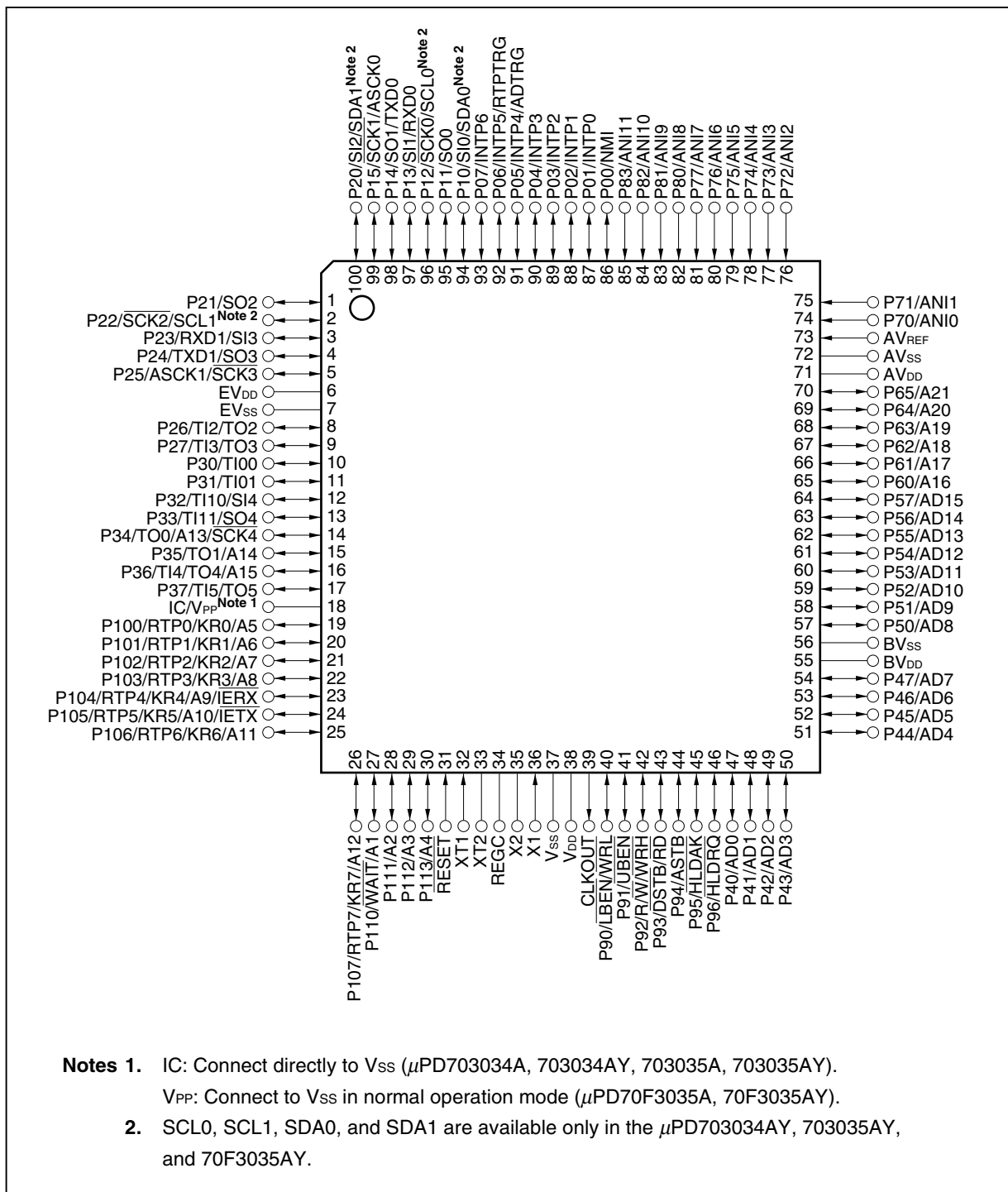
Part Number	Package	Internal ROM
μPD703034AGC-xxx-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Mask ROM (128 KB)
μPD703034AYGC-xxx-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Mask ROM (128 KB)
μPD703034AGF-xxx-3BA	100-pin plastic QFP (14 × 20)	Mask ROM (128 KB)
μPD703034AYGF-xxx-3BA	100-pin plastic QFP (14 × 20)	Mask ROM (128 KB)
μPD703035AGC-xxx-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Mask ROM (256 KB)
μPD703035AYGC-xxx-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Mask ROM (256 KB)
μPD703035AGF-xxx-3BA	100-pin plastic QFP (14 × 20)	Mask ROM (256 KB)
μPD703035AYGF-xxx-3BA	100-pin plastic QFP (14 × 20)	Mask ROM (256 KB)
★ μPD70F3035AGC-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Flash memory (256 KB)
★ μPD70F3035AYGC-8EU	100-pin plastic LQFP (fine pitch) (14 × 14)	Flash memory (256 KB)
★ μPD70F3035AGF-3BA	100-pin plastic QFP (14 × 20)	Flash memory (256 KB)
★ μPD70F3035AYGF-3BA	100-pin plastic QFP (14 × 20)	Flash memory (256 KB)

- Remarks**
1. xxx indicates ROM code suffix.
 2. ROMless versions are not provided.

PIN CONFIGURATION (Top View)

100-pin plastic LQFP (fine pitch) (14 × 14)

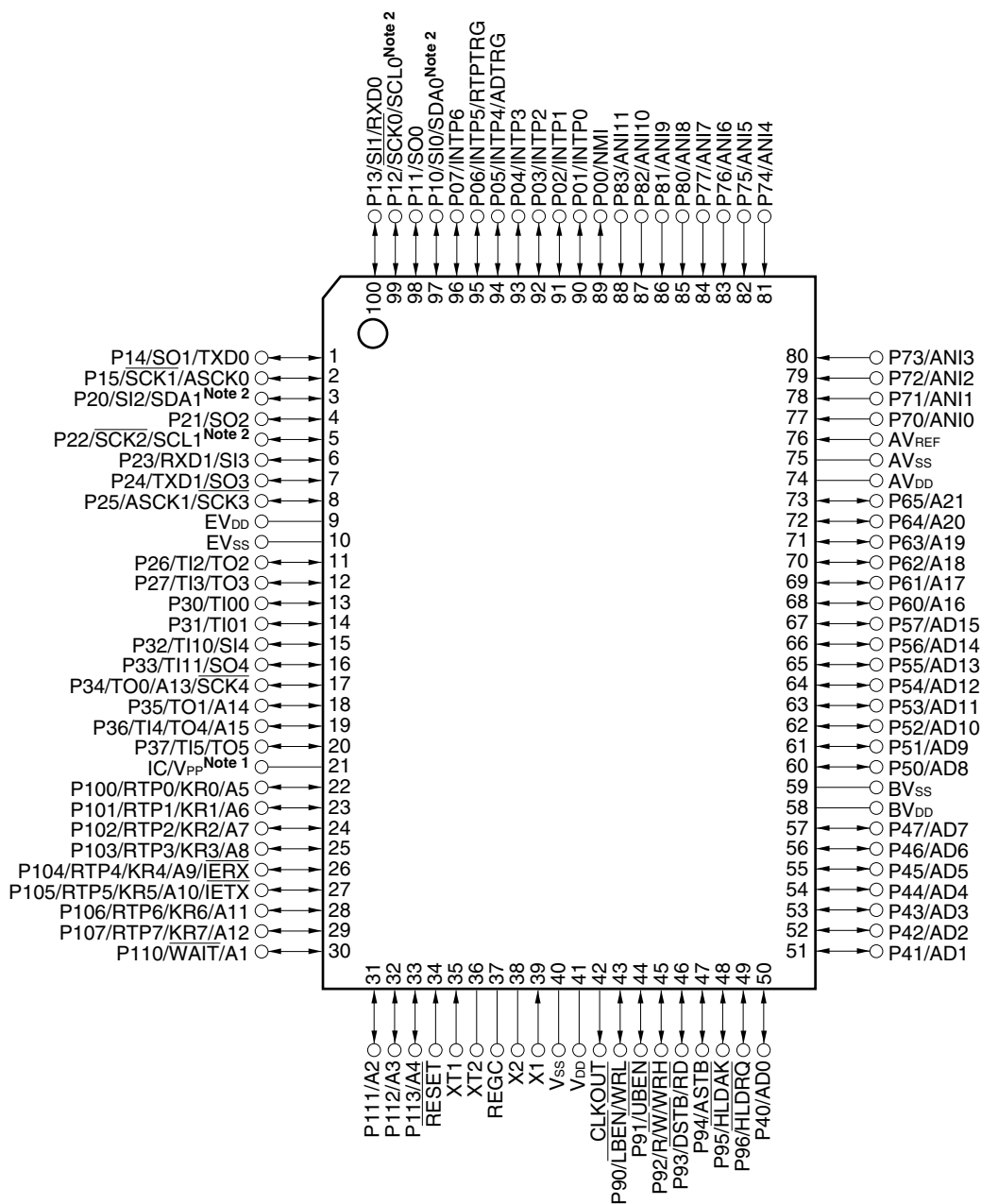
- μPD703034AGC-xxx-8EU
- μPD703034AYGC-xxx-8EU
- μPD703035AGC-xxx-8EU
- μPD703035AYGC-xxx-8EU
- μPD70F3035AGC-8EU
- μPD70F3035AYGC-8EU



- Notes 1.** IC: Connect directly to V_{SS} (μPD703034A, 703034AY, 703035A, 703035AY).
V_{PP}: Connect to V_{SS} in normal operation mode (μPD70F3035A, 70F3035AY).
- 2.** SCL0, SCL1, SDA0, and SDA1 are available only in the μPD703034AY, 703035AY, and 70F3035AY.

100-pin plastic QFP (14 × 20)

- μPD703034AGF-xxx-3BA
- μPD703034AYGF-xxx-3BA
- μPD703035AGF-xxx-3BA
- μPD703035AYGF-xxx-3BA
- μPD70F3035AGF-3BA
- μPD70F3035AYGF-3BA

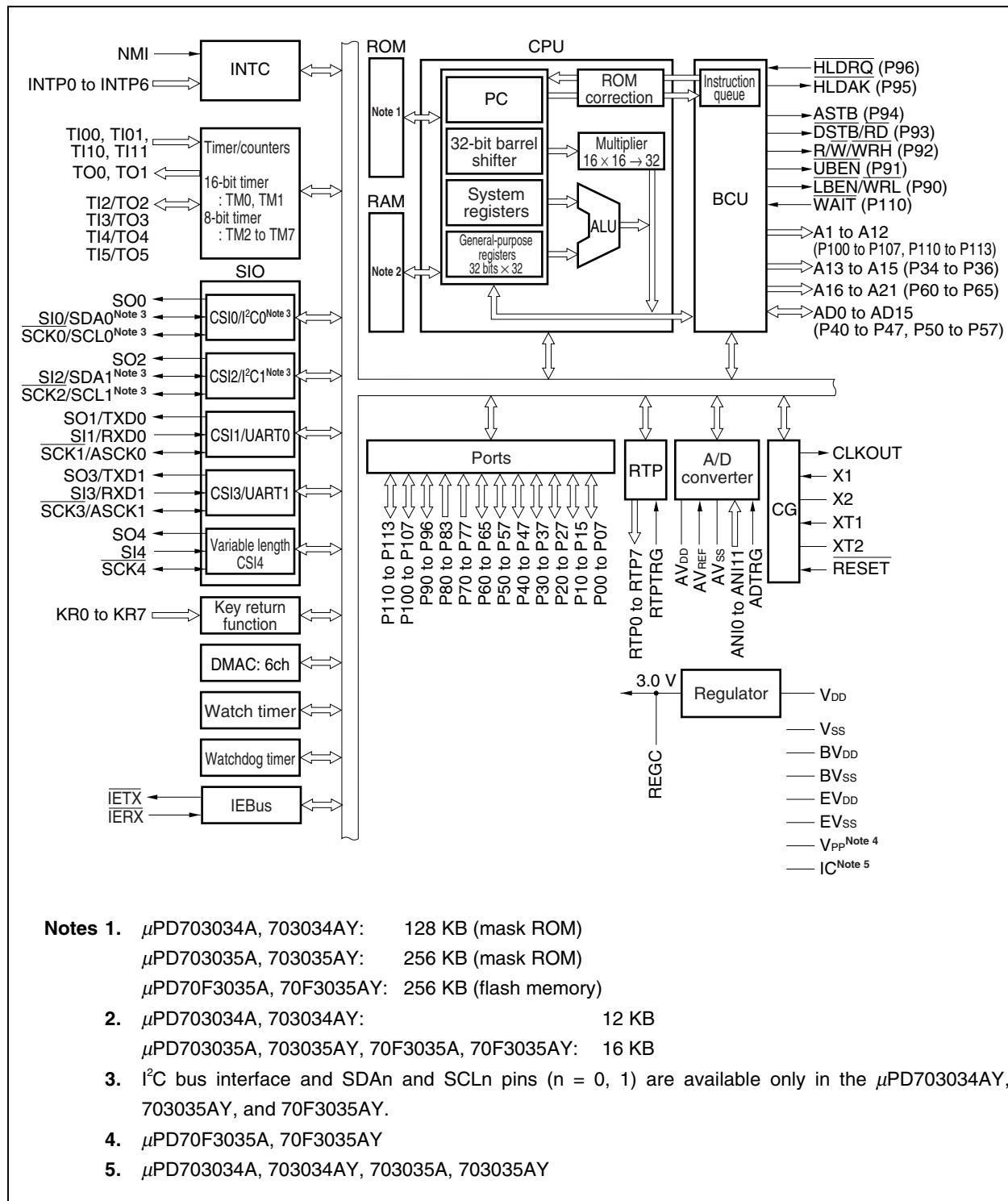


- Notes 1.** IC: Connect directly to Vss (μPD703034A, 703034AY, 703035A, 703035AY).
 VPP: Connect to Vss in normal operation mode (μPD70F3035A, 70F3035AY).
- 2.** SCL0, SCL1, SDA0, and SDA1 are available only in the μPD703034AY, 703035AY, and 70F3035AY.

PIN IDENTIFICATION

A1 to A21:	Address Bus	P70 to P77:	Port 7
AD0 to AD15:	Address/Data Bus	P80 to P83:	Port 8
ADTRG:	AD Trigger Input	P90 to P96:	Port 9
ANI0 to ANI11:	Analog Input	P100 to P107:	Port 10
ASCK0, ASCK1:	Asynchronous Serial Clock	P110 to P113:	Port 11
ASTB:	Address Strobe	\overline{RD} :	Read
AV _{DD} :	Analog Power Supply	\overline{REGC} :	Regulator Clock
AV _{REF} :	Analog Reference Voltage	\overline{RESET} :	Reset
AV _{SS} :	Analog Ground	RTP0 to RTP7:	Real-time Output Port
BV _{DD} :	Power Supply for Bus Interface	RTPTRG:	RTP Trigger Input
BV _{SS} :	Ground for Bus Interface	R/W:	Read/Write Status
CLKOUT:	Clock Output	$\overline{RXD0}$, $\overline{RXD1}$:	Receive Data
\overline{DSTB} :	Data Strobe	$\overline{SCK0}$ to $\overline{SCK4}$:	Serial Clock
EV _{DD} :	Power Supply for Port	SCL0, SCL1:	Serial Clock
EV _{SS} :	Ground for Port	SDA0, SDA1:	Serial Data
\overline{HLDK} :	Hold Acknowledge	SI0 to SI4:	Serial Input
\overline{HLDRQ} :	Hold Request	SO0 to SO4:	Serial Output
IC:	Internally Connected	TI00, TI01, TI10, :	Timer Input
\overline{IERX} :	IEBus Receive Data	TI11, TI2 to TI5	
\overline{IETX} :	IEBus Transmit Data	TO0 to TO5:	Timer Output
INTP0 to INTP6:	Interrupt Request from Peripherals	$\overline{TXD0}$, $\overline{TXD1}$:	Transmit Data
KR0 to KR7:	Key Return	\overline{UBEN} :	Upper Byte Enable
\overline{LBEN} :	Lower Byte Enable	V _{DD} :	Power Supply
NMI:	Non-Maskable Interrupt Request	V _{PP} :	Programming Power Supply
P00 to P07:	Port 0	V _{SS} :	Ground
P10 to P15:	Port 1	\overline{WAIT} :	Wait
P20 to P27:	Port 2	\overline{WRH} :	Write Strobe High Level Data
P30 to P37:	Port 3	\overline{WRL} :	Write Strobe Low Level Data
P40 to P47:	Port 4	X1, X2:	Crystal for Main Clock
P50 to P57:	Port 5	XT1, XT2:	Crystal for Sub-clock
P60 to P65:	Port 6		

INTERNAL BLOCK DIAGRAM



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1. DIFFERENCES AMONG PRODUCTS

Product Name	Incorporated I°C	ROM		RAM Size	Flash Memory Programming Pin	Package
		Type	Size			
μPD703034A	No	Mask ROM	128 KB	12 KB	No	100-pin QFP (14 × 20) 100-pin LQFP (14 × 14)
μPD703034AY	Yes					
μPD703035A	No	Mask ROM	256 KB	16 KB	No	100-pin QFP (14 × 20) 100-pin LQFP (14 × 14)
μPD703035AY	Yes					
μPD70F3035A	No	Flash memory			Yes (V _{PP})	
μPD70F3035AY	Yes					
μPD703037A	No	Mask ROM	512 KB	24 KB	No	100-pin QFP (14 × 20)
μPD703037AY	Yes					
μPD70F3037A	No	Flash memory			Yes (V _{PP})	
μPD70F3037AY	Yes					

- Cautions 1.** There are differences in noise immunity and noise radiation between the flash memory and mask ROM versions. When pre-producing an application set with the flash memory version and then mass-producing it with the mask ROM version, be sure to conduct sufficient evaluations for the commercial samples (not engineering samples) of the mask ROM version.
- 2.** When replacing the flash memory versions with mask ROM versions, write the same code in the empty area of the internal ROM.

2. PIN FUNCTIONS

2.1 Port Pins

(1/2)

Pin Name	I/O	PULL	Function	Alternate Function
P00	I/O	Yes	Port 0 8-bit I/O port Input/output can be specified in 1-bit units.	NMI
P01				INTP0
P02				INTP1
P03				INTP2
P04				INTP3
P05				INTP4/ADTRG
P06				INTP5/RTPTRG
P07				INTP6
P10	I/O	Yes	Port 1 6-bit I/O port Input/output can be specified in 1-bit units.	SI0/SDA0 ^{Note}
P11				SO0
P12				SCK0/SCL0 ^{Note}
P13				SI1/RXD0
P14				SO1/TXD0
P15				SCK1/ASCK0
P20	I/O	Yes	Port 2 8-bit I/O port Input/output can be specified in 1-bit units.	SI2/SDA1 ^{Note}
P21				SO2
P22				SCK2/SCL1 ^{Note}
P23				SI3/RXD1
P24				SO3/TXD1
P25				SCK3/ASCK1
P26				TI2/TO2
P27				TI3/TO3
P30	I/O	Yes	Port 3 8-bit I/O port Input/output can be specified in 1-bit units.	TI00
P31				TI01
P32				TI10/SI4
P33				TI11/SO4
P34				TO0/A13/SCK4
P35				TO1/A14
P36				TI4/TO4/A15
P37				TI5/TO5
P40 to P47	I/O	No	Port 4 8-bit I/O port Input/output can be specified in 1-bit units.	AD0 to AD7
P50 to P57	I/O	No	Port 5 8-bit I/O port Input/output can be specified in 1-bit units.	AD8 to AD15

Note μPD703034AY, 703035AY, 70F3035AY only.

Remark PULL: On-chip pull-up resistor

(2/2)

Pin Name	I/O	PULL	Function	Alternate Function
P60 to P65	I/O	No	Port 6 6-bit I/O port Input/output can be specified in 1-bit units.	A16 to A21
P70 to P77	Input	No	Port 7 8-bit input port	ANI0 to ANI7
P80 to P83	Input	No	Port 8 4-bit input port	ANI8 to ANI11
P90	I/O	No	Port 9 7-bit I/O port Input/output can be specified in 1-bit units.	$\overline{\text{LBEN}}/\overline{\text{WRL}}$
P91				$\overline{\text{UBEN}}$
P92				$\overline{\text{R/W}}/\overline{\text{WRH}}$
P93				$\overline{\text{DSTB}}/\overline{\text{RD}}$
P94				ASTB
P95				$\overline{\text{HLDAK}}$
P96				$\overline{\text{HLDRQ}}$
P100	I/O	Yes	Port 10 8-bit I/O port Input/output can be specified in 1-bit units.	RTP0/A5/KR0
P101				RTP1/A6/KR1
P102				RTP2/A7/KR2
P103				RTP3/A8/KR3
P104				RTP4/A9/KR4/ $\overline{\text{IERX}}$
P105				RTP5/A10/KR5/ $\overline{\text{IETX}}$
P106				RTP6/A11/KR6
P107				RTP7/A12/KR7
P110	I/O	Yes	Port 11 4-bit I/O port Input/output can be specified in 1-bit units.	$\text{A1}/\overline{\text{WAIT}}$
P111				A2
P112				A3
P113				A4

Remark PULL: On-chip pull-up resistor

2.2 Non-Port Pins

(1/4)

Pin Name	I/O	PULL	Function	Alternate Function
A1	Output	Yes	Lower address bus used for external memory expansion	P110/ $\overline{\text{WAIT}}$
A2				P111
A3				P112
A4				P113
A5				P100/RTP0/KR0
A6				P101/RTP1/KR1
A7				P102/RTP2/KR2
A8				P103/RTP3/KR3
A9				P104/RTP4/KR4/ $\overline{\text{IERX}}$
A10				P105/RTP5/KR5/ $\overline{\text{IETX}}$
A11				P106/RTP6/KR6
A12				P107/RTP7/KR7
A13				P34/TO0/ $\overline{\text{SCK4}}$
A14				P35/TO1
A15				P36/TO4/TI4
A16 to A21	Output	No	Higher address bus used for external memory expansion	P60 to P65
AD0 to AD7	I/O	No	16-bit multiplexed address/data bus used for external memory expansion	P40 to P47
AD8 to AD15				P50 to P57
ADTRG	Input	Yes	A/D converter external trigger input	P05/ $\overline{\text{INTP4}}$
ANI0 to ANI7	Input	No	Analog input to A/D converter	P70 to P77
ANI8 to ANI11				P80 to P83
ASCK0	Input	Yes	Baud rate clock input for UART0	P15/ $\overline{\text{SCK1}}$
ASCK1			Baud rate clock input for UART1	P25/ $\overline{\text{SCK3}}$
ASTB	Output	No	External address strobe output	P94
AV _{DD}	–	–	Positive power supply for A/D converter and alternate port	–
AV _{REF}	Input	–	Reference voltage input for A/D converter	–
AV _{SS}	–	–	Ground potential for A/D converter and alternate port	–
BV _{DD}	–	–	Positive power supply for bus interface and alternate port	–
BV _{SS}	–	–	Ground potential for bus interface and alternate port	–
CLKOUT	Output	–	Internal system clock output	–
DSTB	Output	No	External data strobe output	P93/ $\overline{\text{RD}}$
EV _{DD}	–	–	Positive power supply for I/O ports and alternate-function pins (except bus interface alternate port)	–
EV _{SS}	–	–	Ground potential for I/O ports and alternate-function pins (except bus interface alternate port)	–
$\overline{\text{HLDAK}}$	Output	No	Bus hold acknowledge output	P95
$\overline{\text{HLDRQ}}$	Input	No	Bus hold request input	P96
IC	–	–	Internally connected (μPD703034A, 703034AY, 703035A, 703035AY only)	–

Remark PULL: On-chip pull-up resistor

(2/4)

Pin Name	I/O	PULL	Function	Alternate Function
$\overline{\text{IERX}}$	Input	Yes	IEBus data input	P104/RTP4/A9/KR4
$\overline{\text{IETX}}$	Output		IEBus data output	P105/RTP5/A10/KR5
INTP0	Input	Yes	External interrupt request input (analog noise elimination)	P01
INTP1				P02
INTP2				P03
INTP3				P04
INTP4	Input	Yes	External interrupt request input (digital noise elimination)	P05/ADTRG
INTP5				P06/RTPTRG
INTP6	Input	Yes	External interrupt request input (digital noise elimination supporting remote controller)	P07
KR0	Input	Yes	Key return input	P100/RTP0/A5
KR1				P101/RTP1/A6
KR2				P102/RTP2/A7
KR3				P103/RTP3/A8
KR4				P104/RTP4/A9/ $\overline{\text{IERX}}$
KR5				P105/RTP5/A10/ $\overline{\text{IETX}}$
KR6				P106/RTP6/A11
KR7				P107/RTP7/A12
$\overline{\text{LBEN}}$	Output	No	External data bus's lower byte enable output	P90/ $\overline{\text{WRL}}$
NMI	Input	Yes	Non-maskable interrupt request input	P00
$\overline{\text{RD}}$	Output	No	Read strobe output	P93/ $\overline{\text{DSTB}}$
REGC	–	–	Regulator output stabilization capacitance connection	–
$\overline{\text{RESET}}$	Input	–	System reset input	–
RTP0	Output	Yes	Real-time output port	P100/KR0/A5
RTP1				P101/KR1/A6
RTP2				P102/KR2/A7
RTP3				P103/KR3/A8
RTP4				P104/KR4/A9/ $\overline{\text{IERX}}$
RTP5				P105/KR5/A10/ $\overline{\text{IETX}}$
RTP6				P106/KR6/A11
RTP7				P107/KR7/A12
RTPTRG	Input	Yes	Real-time output port external trigger input	P06/INTP5
$\overline{\text{R/W}}$	Output	No	External read/write status output	P92/ $\overline{\text{WRH}}$
RXD0	Input	Yes	Serial receive data input for UART0 and UART1	P13/SI1
RXD1				P23/SI3

Remark PULL: On-chip pull-up resistor

Pin Name	I/O	PULL	Function	Alternate Function
SCK0	I/O	Yes	Serial clock I/O (3-wire type) for CSI0 to CSI3	P12/SCL0
SCK1				P15/ASCK0
SCK2				P22/SCL1
SCK3				P25/ASCK1
SCK4	I/O	Yes	Serial clock I/O (3-wire type) for variable length CSI4	P34/TO0/A13
SCL0	I/O	Yes	Serial clock I/O for I ² C0 and I ² C1 (μPD703034AY, 703035AY, 70F3035AY only)	P12/SCK0
SCL1				P22/SCK2
SDA0	I/O	Yes	Serial transmit/receive data I/O for I ² C0 and I ² C1 (μPD703034AY, 703035AY, 70F3035AY only)	P10/SI0
SDA1				P20/SI2
SI0	Input	Yes	Serial receive data input (3-wire type) for CSI0 to CSI3	P10/SDA0
SI1				P13/RXD0
SI2				P20/SDA1
SI3				P23/RXD1
SI4	Input	Yes	Serial receive data input (3-wire type) for variable length CSI4	P32/TI10
SO0	Output	Yes	Serial transmit data output (3-wire type) for CSI0 to CSI3	P11
SO1				P14/TXD0
SO2				P21
SO3				P24/TXD1
SO4	Output	Yes	Serial transmit data output (3-wire type) for variable length CSI4	P33/TI11
TI00	Input	Yes	External count clock input for TM0/external capture trigger input for TM0	P30
TI01			External capture trigger input for TM0	P31
TI10			External count clock input for TM1/external capture trigger input for TM1	P32/SI4
TI11			External capture trigger input for TM1	P33/SO4
TI2	Input	Yes	External count clock input for TM2 to TM5	P26/TO2
TI3				P27/TO3
TI4				P36/TO4/A15
TI5				P37/TO5
TO0	Output	Yes	Pulse signal output for TM0 and TM1	P34/A13/SCK4
TO1				P35/A14
TO2	Output	Yes	Pulse signal output for TM2 to TM5	P26/TI2
TO3				P27/TI3
TO4				P36/TI4/A15
TO5				P37/TI5
TXD0	Output	Yes	Serial transmit data output for UART0 and UART1	P14/SO1
TXD1				P24/SO3
UBEN	Output	No	Higher byte enable output for external data bus	P91
V _{DD}	–	–	Positive power supply pin	–

Remark PULL: On-chip pull-up resistor

(4/4)

Pin Name	I/O	PULL	Function	Alternate Function
V _{PP}	–	–	High voltage apply pin for program write/verify (μ PD70F3035A, 70F3035AY only)	–
V _{SS}	–	–	Ground potential	–
$\overline{\text{WAIT}}$	Input	Yes	Control signal input for inserting wait in bus cycle	P110/A1
$\overline{\text{WRH}}$	Output	No	Higher byte write strobe signal output for external data bus	P92/R $\overline{\text{W}}$
$\overline{\text{WRL}}$	Output	No	Lower byte write strobe signal output for external data bus	P90/LBEN
X1	Input	No	Resonator connection for main clock	–
X2	–			–
XT1	Input	No	Resonator connection for subsystem clock	–
XT2	–			–

Remark PULL: On-chip pull-up resistor

2.3 Pin I/O Circuits and Recommended Connection of Unused Pins

The input/output circuit type of each pin and recommended connection of unused pins are show in Table 2-1. For the input/output schematic circuit diagram of each type, refer to Figure 2-1.

Table 2-1. Types of Pin I/O Circuits (1/2)

Pin	Alternate Function	I/O Circuit Type	I/O Buffer Power Supply	Recommended Connection of Unused Pins
P00	NMI	8-A	EV _{DD}	Input state: Independently connect to EV _{DD} or EV _{SS} via a resistor. Output state: Leave open.
P01	INTP0			
P02	INTP1			
P03	INTP2			
P04	INTP3			
P05	INTP4/ADTRG			
P06	INTP5/RTPTRG			
P07	INTP6			
P10	SI0/SDA0	10-A	EV _{DD}	Input state: Independently connect to EV _{DD} or EV _{SS} via a resistor. Output state: Leave open.
P11	SO0	26		
P12	SCK0/SCL0	10-A		
P13	SI1/RXD0	8-A		
P14	SO1/TXD0	26		
P15	SCK1/ASCK0	10-A		
P20	SI2/SDA1	10-A	EV _{DD}	Input state: Independently connect to EV _{DD} or EV _{SS} via a resistor. Output state: Leave open.
P21	SO2	26		
P22	SCK2/SCL1	10-A		
P23	SI3/RXD1	8-A		
P24	SO3/TXD1	26		
P25	SCK3/ASCK1	10-A		
P26	TI2/TO2	8-A		
P27	TI3/TO3			
P30	TI00	8-A	EV _{DD}	Input state: Independently connect to EV _{DD} or EV _{SS} via a resistor. Output state: Leave open.
P31	TI01			
P32	TI10/SI4			
P33	TI11/SO4			
P34	TO0/A13/SCK4			
P35	TO1/A14	5-A		
P36	TI4/TO4/A15	8-A		
P37	TI5/TO5			
P40 to P47	AD0 to AD7	5	BV _{DD}	Input state: Independently connect to BV _{DD} or BV _{SS} via a resistor. Output state: Leave open.
P50 to P57	AD8 to AD15	5	BV _{DD}	
P60 to P65	A16 to A21	5	BV _{DD}	

★

Table 2-1. Types of Pin I/O Circuits (2/2)

Pin	Alternate Function	I/O Circuit Type	I/O Buffer Power Supply	Recommended Connection of Unused Pins
P70 to P77	ANI0 to ANI7	9	AV _{DD}	Independently connect to AV _{DD} or AV _{SS} via a resistor.
P80 to P83	ANI8 to ANI11	9	AV _{DD}	
P90	$\overline{\text{LBEN}}/\overline{\text{WRL}}$	5	BV _{DD}	Input state: Independently connect to BV _{DD} or BV _{SS} via a resistor. Output state: Leave open.
P91	$\overline{\text{UBEN}}$			
P92	R/W/WRH			
P93	$\overline{\text{DSTB}}/\overline{\text{RD}}$			
P94	ASTB			
★ P95	$\overline{\text{HLDK}}$			
★ P96	$\overline{\text{HLDRQ}}$			
P100	RTP0/A5/KR0	10-A	EV _{DD}	Input state: Independently connect to EV _{DD} or EV _{SS} via a resistor. Output state: Leave open.
P101	RTP1/A6/KR1			
P102	RTP2/A7/KR2			
P103	RTP3/A8/KR3			
P104	RTP4/A9/KR4/ $\overline{\text{IERX}}$			
P105	RTP5/A10/KR5/ $\overline{\text{IETX}}$			
P106	RTP6/A11/KR6			
P107	RTP7/A12/KR7			
P110	A1/ $\overline{\text{WAIT}}$	5-A	EV _{DD}	Input state: Independently connect to EV _{DD} or EV _{SS} via a resistor. Output state: Leave open.
P111	A2			
P112	A3			
P113	A4			
CLKOUT	–	4	BV _{DD}	Leave open.
$\overline{\text{RESET}}$	–	2	EV _{DD}	–
XT1	–	16	–	Connect to V _{SS} via a resistor.
XT2	–	16	–	Leave open.
AV _{REF}	–	–	–	Connect to AV _{SS} via a resistor.
IC ^{Note 1}	–	–	–	Connect directly to V _{SS} .
V _{PP} ^{Note 2}	–	–	–	Connect to V _{SS} .

Notes 1. μPD703034A, 703034AY, 703035A, 703035AY

2. μPD70F3035A, 70F3035AY

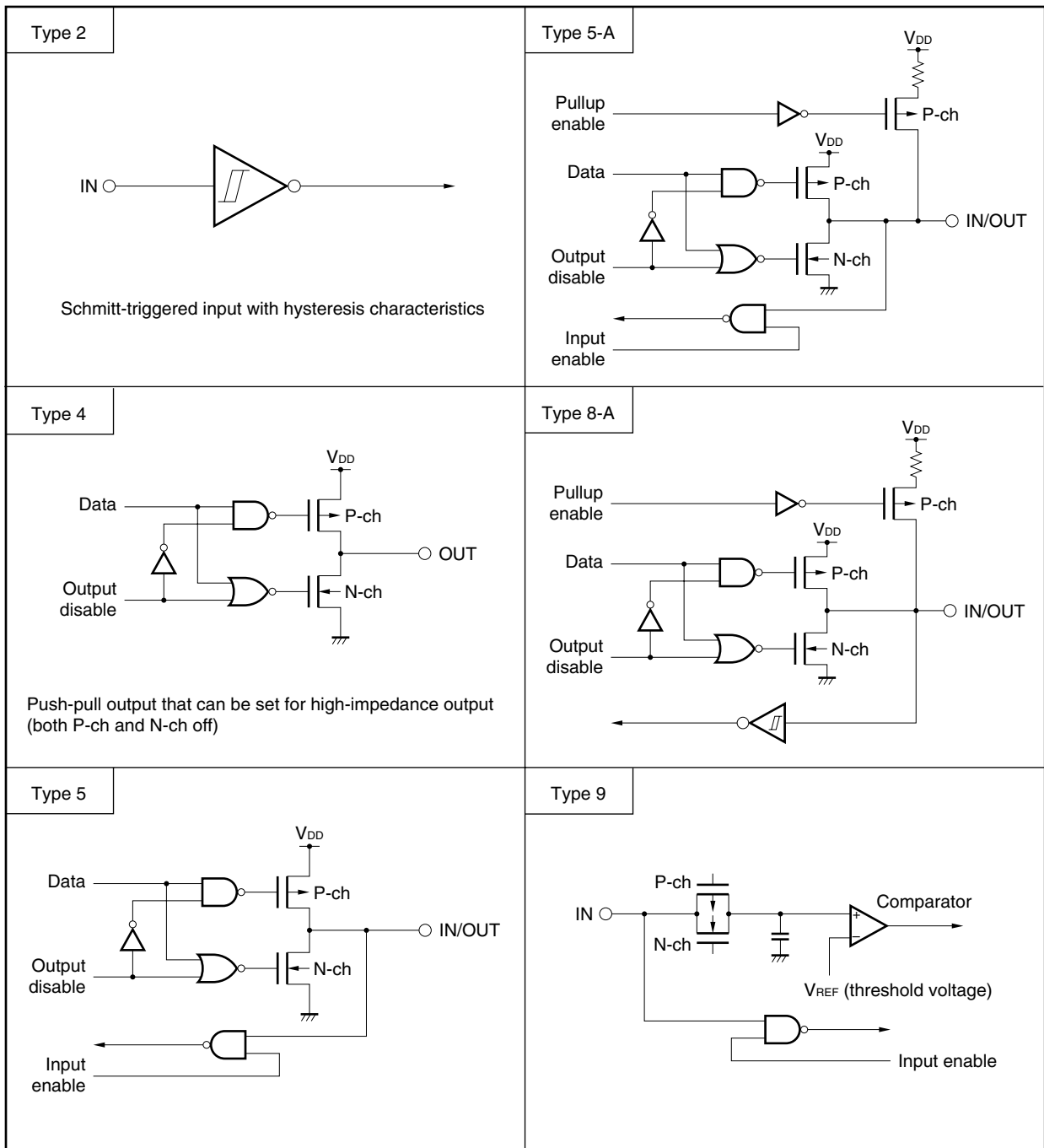
Caution Three power supply systems are available to supply power to the I/O buffers of the V850/SB2's pins: EV_{DD}, BV_{DD}, and AV_{DD}. The voltage ranges that can be used for these I/O buffer power supplies are shown below.

EV_{DD}, BV_{DD}: 3.0 V to 5.5 V

AV_{DD}: 4.5 V to 5.5 V

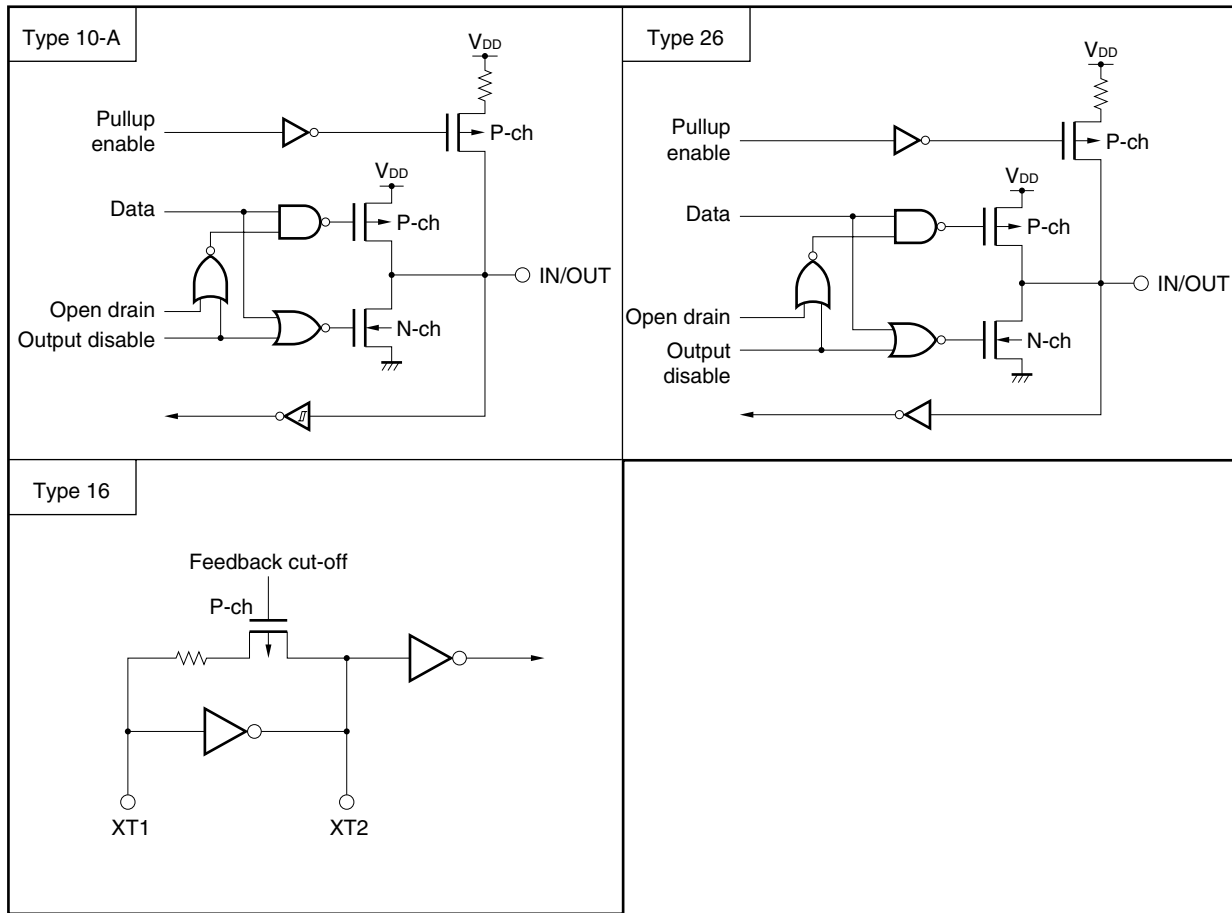
The electrical specifications differ depending on whether the power supply voltage range is 3.0 V to under 4.0 V, or 4.0 V to 5.5 V.

Figure 2-1. Pin Input/Output Circuits (1/2)



Caution V_{DD} in the circuit diagrams can be read as EV_{DD} , BV_{DD} , or AV_{DD} , as appropriate.

Figure 2-1. Pin Input/Output Circuits (2/2)



Caution V_{DD} in the circuit diagrams can be read as EV_{DD} , BV_{DD} , or AV_{DD} , as appropriate.

3. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings (T_A = 25°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V _{DD}	V _{DD} pin	-0.5 to +7.0	V
	V _{PP}	μPD70F3035A, 70F3035AY only	-0.5 to +8.5	V
	AV _{DD}	AV _{DD} pin	-0.5 to +7.0	V
	BV _{DD}	BV _{DD} pin	-0.5 to +7.0	V
	EV _{DD}	EV _{DD} pin	-0.5 to +7.0	V
	AV _{SS}	AV _{SS} pin	-0.5 to +0.5	V
	BV _{SS}	BV _{SS} pin	-0.5 to +0.5	V
	EV _{SS}	EV _{SS} pin	-0.5 to +0.5	V
Input voltage	V _{I1}	Note 1 (BV _{DD} pin)	-0.5 to BV _{DD} + 0.5 ^{Note 4}	V
	V _{I2}	Note 2 , RESET (EV _{DD} pin)	-0.5 to EV _{DD} + 0.5 ^{Note 4}	V
Analog input voltage	V _{IAN}	Note 3 (AV _{DD} pin)	-0.5 to AV _{DD} + 0.5 ^{Note 4}	V
Analog reference input voltage	AV _{REF}	AV _{REF} pin	-0.5 to AV _{DD} + 0.5 ^{Note 4}	V
Output current, low	I _{OL}	Per pin	4.0	mA
		Total for P00 to P07, P10 to P15, P20 to P25	25	mA
		Total for P26, P27, P30 to P37, P100 to P107, P110 to P113	25	mA
		Total for P40 to P47, P90 to P96, CLKOUT	25	mA
		Total for P50 to P57, P60 to P65	25	mA
Output current, high	I _{OH}	Per pin	-4.0	mA
		Total for P00 to P07, P10 to P15, P20 to P25	-25	mA
		Total for P26, P27, P30 to P37, P100 to P107, P110 to P113	-25	mA
		Total for P40 to P47, P90 to P96, CLKOUT	-25	mA
		Total for P50 to P57, P60 to P65	-25	mA
Output voltage	V _{O1}	Note 1 , CLKOUT (BV _{DD} pin)	-0.5 to BV _{DD} + 0.5 ^{Note 4}	V
	V _{O2}	Note 2 (EV _{DD} pin)	-0.5 to EV _{DD} + 0.5 ^{Note 4}	V
Operating ambient temperature	T _A	Normal operation mode	-40 to +85	°C
		Flash memory programming mode (μPD70F3035A, 70F3035AY only)	Note 5	°C
Storage temperature	T _{stg}	μPD703034A, 703034AY	-65 to +150	°C
		μPD703035A, 703035AY		
		μPD70F3035A, 70F3035AY	-40 to +125	°C

Notes 1. Ports 4, 5, 6, 9, and their alternate-function pins

2. Ports 0, 1, 2, 3, 10, 11, and their alternate-function pins

3. Ports 7, 8, and their alternate-function pins

4. Be sure not to exceed the absolute maximum ratings (MAX. value) of each supply voltage.

5. I, K, E rank products: T_A = 10 to 85°C

P rank product: T_A = -20 to +85°C

The rank is indicated by the letter appearing as the 5th digit from the left in the lot number.

- Cautions**
1. Do not directly connect the output (or I/O) pins of IC products to each other, or to V_{DD}, V_{CC}, and GND. Open-drain pins or open-collector pins, however, can be directly connected to each other. Direct connection of the output pins between an IC product and an external circuit is possible, if the output pins can be set to the high-impedance state and the output timing of the external circuit is designed to avoid output conflict.
 2. Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
The ratings and conditions indicated for DC characteristics and AC characteristics represent the quality assurance range during normal operation.

Capacitance (T_A = 25°C, V_{DD} = AV_{DD} = BV_{DD} = EV_{DD} = V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C _i	f _c = 1 MHz Unmeasured pins returned to 0 V			15	pF
I/O capacitance	C _{io}				15	pF
Output capacitance	C _o				15	pF

Operating Conditions

★ (1) Operating frequency

Operating Frequency (f _{xx})		V _{DD}	AV _{DD}		BV _{DD}	EV _{DD}	Remark
			Note 1	Note 2			
2 to 13 MHz		4.0 to 5.5 V	4.5 to 5.5 V	4.0 to 5.5 V	3.0 to 5.5 V	3.0 to 5.5 V	Note 3
32.768 kHz	Other than IDLE mode	4.0 to 5.5 V	4.5 to 5.5 V	4.0 to 5.5 V	3.0 to 5.5 V	3.0 to 5.5 V	–
	IDLE mode	3.5 to 5.5 V	–	4.0 to 5.5 V	3.0 to 5.5 V	3.0 to 5.5 V	Note 4

- Notes**
1. When A/D converter is used
 2. When A/D converter is not used
 3. During STOP mode (when only watch timer is operating), V_{DD} = 3.5 to 5.5 V. Shifting to STOP mode or restoring from STOP mode must be performed at V_{DD} = 4.0 V min.
 4. Shifting to IDLE mode or restoring from IDLE mode must be performed at V_{DD} = 4.0 V min.

(2) CPU operating frequency

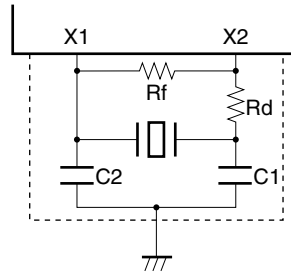
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU operating frequency	f _{CPU}	Main clock operation	0.25		13	MHz
		Subclock operation		32.768		kHz

Recommended Oscillator

(1) Main clock oscillator (T_A = -40 to +85°C)

(a) Connection of ceramic resonator or crystal resonator

★



Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Oscillation frequency	f _{xx}		2		13	MHz
Oscillation stabilization time	–	Upon reset release		2 ¹⁹ /f _{xx}		s
	–	Upon STOP mode release		Note		s

Note The TYP. value differs depending on the setting of the oscillation stabilization time select register (OSTS).

- Cautions**
1. The main clock oscillator operates on the output voltage of the on-chip regulator (3.0 V). External clock input is prohibited.
 2. When using the main clock oscillator, wire as follows in the area enclosed by the broken lines in the above figure to avoid an adverse effect from wiring capacitance.
 - Keep the wiring length as short as possible.
 - Do not cross the wiring with the other signal lines.
 - Do not route the wiring near a signal line through which a high fluctuating current flows.
 - Always make the ground point of the oscillator capacitor the same potential as V_{SS}.
 - Do not ground the capacitor to a ground pattern through which a high current flows.
 - Do not fetch signals from the oscillator.
 3. Ensure that the duty of oscillation waveform is between 5.5 and 4.5.
 4. Sufficiently evaluate the matching between the μPD703034A, 703034AY, 703035A, 703035AY, 70F3035A, 70F3035AY and the resonator.

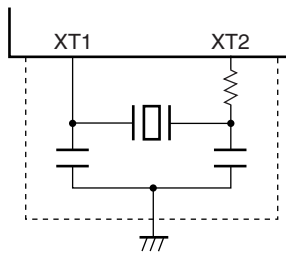
★ (i) Murata Mfg. Co., Ltd.: Ceramic resonator (T_A = -40 to +85°C)

Manufacturer	Part Number	Oscillation Frequency f _{xx} (MHz)	Recommended Circuit Constant				Oscillation Voltage Range	
			C1 (pF)	C2 (pF)	Rf (kΩ)	Rd (kΩ)	MIN. (V)	MAX. (V)
Murata Mfg. Co., Ltd.	CSTLS6M29G53-B0	6.290	On-chip	On-chip	-	0	4.0	5.5
	CSTCR6M29G53-R0		On-chip	On-chip	-	0	4.0	5.5
	CSTLA12M5T55001-B0	12.583	On-chip	On-chip	-	0	4.0	5.5
	CSTCV12M5T54J01-R0		On-chip	On-chip	-	0	4.0	5.5

Caution The oscillator constant and oscillation voltage range indicate conditions of stable oscillation. Oscillation frequency precision is not guaranteed. For applications requiring oscillation frequency precision, the oscillation frequency must be adjusted on the implementation circuit. For details, please contact directly the manufacturer of the resonator you will use.

(2) Subclock oscillator (T_A = -40 to +85°C)

(a) Connection of crystal resonator



Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Oscillation frequency	f _{XT}		32	32.768	35	kHz
Oscillation stabilization time	-			10		s

- Cautions**
- The subclock oscillator operates on the output voltage of the on-chip regulator (3.0 V). External clock input is prohibited.
 - When using the subclock oscillator, wire as follows in the area enclosed by the broken lines in the above figure to avoid an adverse effect from wiring capacitance.
 - Keep the wiring length as short as possible.
 - Do not cross the wiring with the other signal lines.
 - Do not route the wiring near a signal line through which a high fluctuating current flows.
 - Always make the ground point of the oscillator capacitor the same potential as V_{SS}.
 - Do not ground the capacitor to a ground pattern through which a high current flows.
 - Do not fetch signals from the oscillator.
 - Sufficiently evaluate the matching between the μPD703034A, 703034AY, 703035A, 703035AY, 70F3035A, 70F3035AY and the resonator.

DC Characteristics (T_A = -40 to +85°C, V_{DD} = 4.0 to 5.5 V, BV_{DD} = EV_{DD} = 3.0 to 5.5 V,

AV_{DD} = 4.5 to 5.5 V (when A/D converter is used),

AV_{DD} = 4.0 to 5.5 V (when A/D converter is not used), V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Note 1	4.0 V ≤ BV _{DD} ≤ 5.5 V	0.7BV _{DD}		BV _{DD}	V
			3.0 V ≤ BV _{DD} < 4.0 V	0.8BV _{DD}		BV _{DD}	V
	V _{IH2}	Note 2	4.0 V ≤ EV _{DD} ≤ 5.5 V	0.7EV _{DD}		EV _{DD}	V
			3.0 V ≤ EV _{DD} < 4.0 V	0.8EV _{DD}		EV _{DD}	V
	V _{IH3}	Note 3, RESET	4.0 V ≤ EV _{DD} ≤ 5.5 V	0.7EV _{DD}		EV _{DD}	V
3.0 V ≤ EV _{DD} < 4.0 V			0.8EV _{DD}		EV _{DD}	V	
V _{IH4}	Note 4		0.7AV _{DD}		AV _{DD}	V	
Input voltage, low	V _{IL1}	Note 1		BV _{SS}		0.3BV _{DD}	V
	V _{IL2}	Note 2		EV _{SS}		0.3EV _{DD}	V
	V _{IL3}	Note 3, RESET		EV _{SS}		0.3EV _{DD}	V
	V _{IL4}	Note 4		AV _{SS}		0.3AV _{DD}	V
Output voltage, high	V _{OH1}	Note 1, CLKOUT	3.0 V ≤ BV _{DD} ≤ 5.5 V, I _{OH} = -100 μA	BV _{DD} -0.5			V
			4.0 V ≤ BV _{DD} ≤ 5.5 V, I _{OH} = -3 mA	BV _{DD} -1.0			V
	V _{OH2}	Notes 2, 3	3.0 V ≤ EV _{DD} ≤ 5.5 V, I _{OH} = -100 μA	EV _{DD} -0.5			V
			4.0 V ≤ EV _{DD} ≤ 5.5 V, I _{OH} = -3 mA	EV _{DD} -1.0			V
Output voltage, low	V _{OL}	I _{OL} = 3 mA, 3.0 V ≤ BV _{DD} , EV _{DD} ≤ 5.5 V				0.5	V
			I _{OL} = 3 mA, 4.0 V ≤ BV _{DD} , EV _{DD} ≤ 5.5 V				0.4
V _{PP} power supply voltage	V _{PP1}	Normal operation		0		0.54	V
Input leakage current, high	I _{LIH}	V _I = V _{DD} = BV _{DD} = EV _{DD} = AV _{DD}				5	μA
Input leakage current, low	I _{LIL}	V _I = 0 V				-5	μA
Output leakage current, high	I _{LOH}	V _O = V _{DD} = BV _{DD} = EV _{DD} = AV _{DD}				5	μA
Output leakage current, low	I _{LOL}	V _O = 0 V				-5	μA

★

Notes 1. Ports 4, 5, 6, 9, and their alternate-function pins

2. P11, P14, P21, P24, P34, P35, P110 to P113, and their alternate-function pins

3. P00 to P07, P10, P12, P13, P15, P20, P22, P23, P25 to P27, P30 to P33, P36, P37, P100 to P107, and their alternate-function pins

4. Ports 7, 8, and their alternate-function pins

DC Characteristics (T_A = -40 to +85°C, V_{DD} = 4.0 to 5.5 V, BV_{DD} = EV_{DD} = 3.0 to 5.5 V,

AV_{DD} = 4.5 to 5.5 V (when A/D converter is used),

AV_{DD} = 4.0 to 5.5 V (when A/D converter is not used), V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Supply current	μPD703034A, μPD703034AY, μPD703035A, μPD703035AY	I _{DD1}	In normal operation mode ^{Note 1}		15	25	mA
		I _{DD2}	In HALT mode ^{Note 1}		6	13	mA
		I _{DD3}	In IDLE mode ^{Note 2}	Watch timer operating	1	4	mA
		I _{DD4}	In STOP mode	Watch timer, subclock oscillator operating	13	70	μA
				Subclock oscillator stopped, XT1 = V _{SS}	8	70	μA
		I _{DD5}	In normal operation mode (subclock operation) ^{Note 3}		50	150	μA
	I _{DD6}	In IDLE mode (subclock operation) ^{Note 3}		13	70	μA	
	μPD70F3035A, μPD70F3035AY	I _{DD1}	In normal operation mode ^{Note 1}		25	48	mA
		I _{DD2}	In HALT mode ^{Note 1}		7	15	mA
		I _{DD3}	In IDLE mode ^{Note 2}	Watch timer operating	1	4	mA
		I _{DD4}	In STOP mode	Watch timer, subclock oscillator operating	13	100	μA
				Subclock oscillator stopped, XT1 = V _{SS}	8	100	μA
		I _{DD5}	In normal operation mode (subclock operation) ^{Note 3}		200	600	μA
	I _{DD6}	In IDLE mode (subclock operation) ^{Note 3}		90	180	μA	
Pull-up resistance	R _L	V _{IN} = 0 V	10	30	100	kΩ	

- Notes**
1. f_{CPU} = f_{XX} = 13 MHz, all peripheral functions operating
 2. f_{XX} = 13 MHz
 3. f_{CPU} = f_{XT} = 32.768 kHz, main clock oscillator stopped

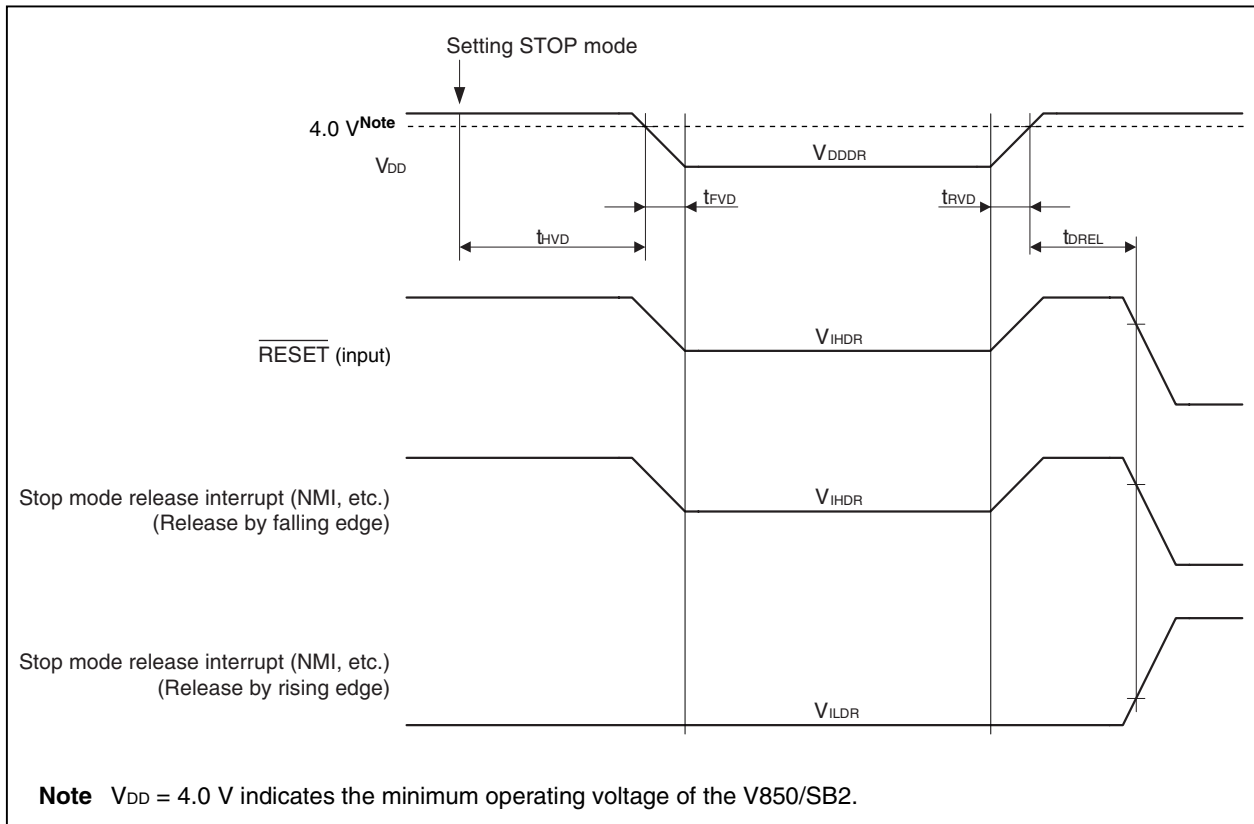
Remark TYP. values are reference values for when T_A = 25°C, V_{DD} = BV_{DD} = EV_{DD} = AV_{DD} = 5.0 V. The current consumed by the output buffer is not included.

Data Retention Characteristics (T_A = -40 to +85°C, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention voltage	V _{DDDR}	STOP mode (all functions not operating)	2.7 ^{Note}		5.5	V
Data retention current	I _{DDDR}	V _{DD} = V _{DDDR} , XT1 = V _{SS} (Subclock stopped)	μPD703034A, μPD703034AY, μPD703035A, μPD703035AY	8	70	μA
			μPD70F3035A, μPD70F3035AY	8	100	μA
Power supply voltage rise time	t _{RV} D		200			μs
Power supply voltage fall time	t _{FV} D		200			μs
Power supply voltage hold time (from STOP mode setting)	t _{HV} D		0			ms
STOP mode release signal input time	t _{DREL}		0			ms
Data retention high-level input voltage	V _{IHDR}	All input ports	0.9V _{DDDR}		V _{DDDR}	V
Data retention low-level input voltage	V _{ILDR}	All input ports	0		0.1V _{DDDR}	V

Note During STOP mode (when only watch timer is operating), V_{DD} = 3.5 to 5.5 V. Shifting to STOP mode or restoring from STOP mode must be performed at V_{DD} = 4.0 V min.

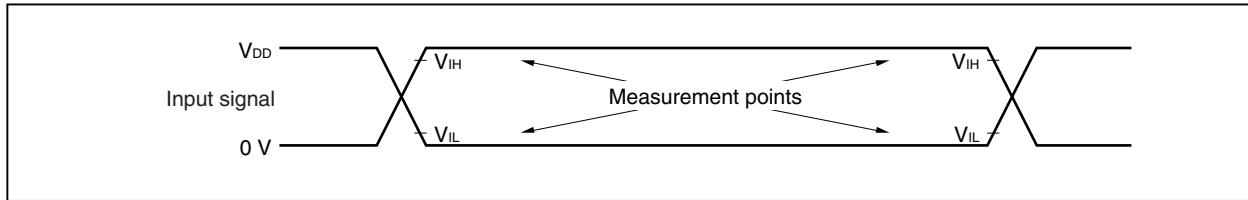
Remark TYP. values are reference values for when T_A = 25°C.



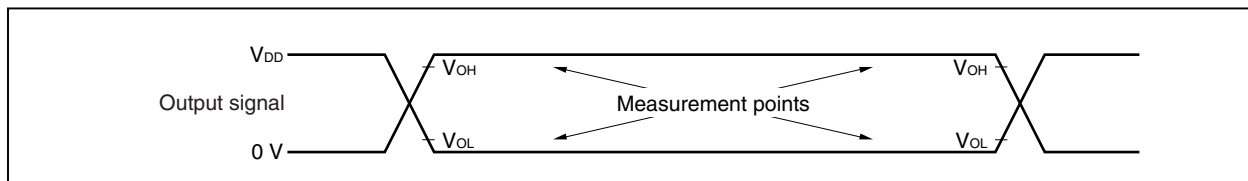
Note V_{DD} = 4.0 V indicates the minimum operating voltage of the V850/SB2.

AC Characteristics ($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V,
 $AV_{DD} = 4.5$ to 5.5 V (when A/D converter is used),
 $AV_{DD} = 4.0$ to 5.5 V (when A/D converter is not used), $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

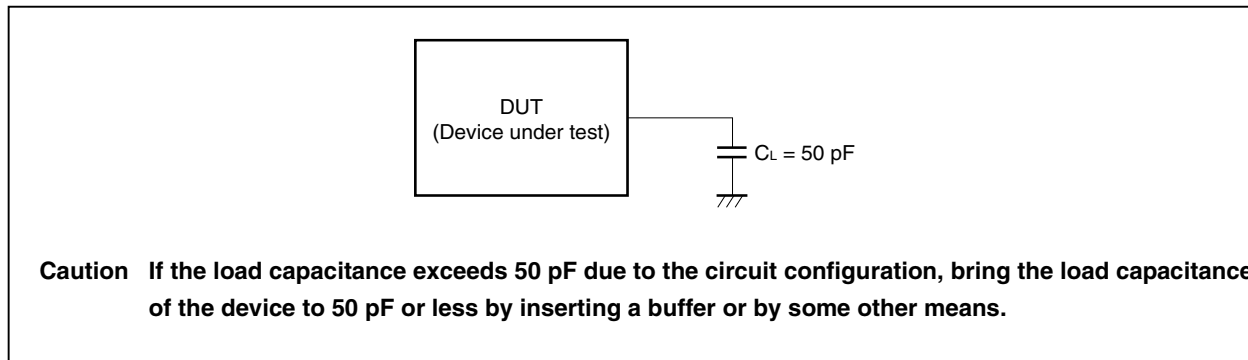
AC Test Input Test Point (V_{DD} : EV_{DD} , BV_{DD} , AV_{DD})



AC Test Output Test Points (V_{DD} : EV_{DD} , BV_{DD})



Load Conditions



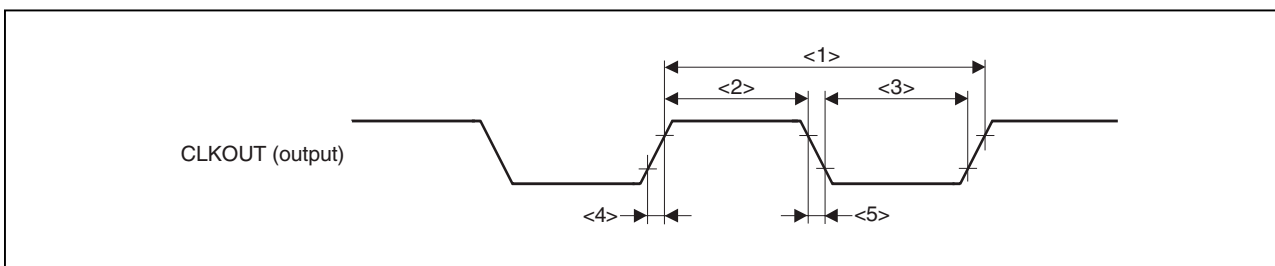
(1) Clock timing

(a) $T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = BV_{DD} = 4.0$ to 5.5 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
CLKOUT output cycle	<1> t_{CYK}		76.9 ns	31.2 μs	
CLKOUT high-level width	<2> t_{WKH}		$0.4t_{CYK} - 12$		ns
CLKOUT low-level width	<3> t_{WKL}		$0.4t_{CYK} - 12$		ns
CLKOUT rise time	<4> t_{KR}			12	ns
CLKOUT fall time	<5> t_{KF}			12	ns

(b) $T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = 3.0$ to 4.0 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
CLKOUT output cycle	<1> t_{CYK}		76.9 ns	31.2 μs	
CLKOUT high-level width	<2> t_{WKH}		$0.4t_{CYK} - 15$		ns
CLKOUT low-level width	<3> t_{WKL}		$0.4t_{CYK} - 15$		ns
CLKOUT rise time	<4> t_{KR}			15	ns
CLKOUT fall time	<5> t_{KF}			15	ns



(2) Output waveform (other than port 4, port 5, port 6, port 9, and CLKOUT)

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = BV_{SS} = EV_{SS} = 0$ V)

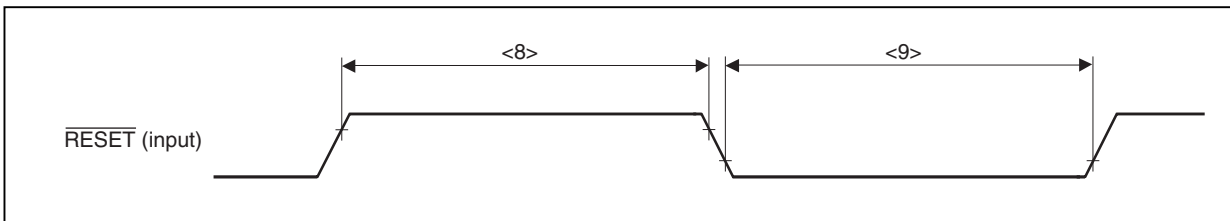
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Output rise time	<6> t_{OR}			20	ns
Output fall time	<7> t_{OF}			20	ns



(3) Reset timing

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
$\overline{\text{RESET}}$ pin high-level width	<8> t_{WRSH}		500		ns
$\overline{\text{RESET}}$ pin low-level width	<9> t_{WRSL}		500		ns



(4) Bus timing

(a) Clock asynchronous ($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = BV_{DD} = 4.0$ to 5.5 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Address setup time (to $ASTB\downarrow$)	<10> t_{SAST}		$0.5T - 16$		ns
Address hold time (from $ASTB\downarrow$)	<11> t_{HSTA}		$0.5T - 15$		ns
Address float delay time from $\overline{DSTB}\downarrow$	<12> t_{FDA}			0	ns
Data input setup time from address	<13> t_{SAID}			$(2 + n)T - 40$	ns
Data input setup time from $\overline{DSTB}\downarrow$	<14> t_{SDID}			$(1 + n)T - 40$	ns
Delay time from $ASTB\downarrow$ to $\overline{DSTB}\downarrow$	<15> t_{DSTD}		$0.5T - 15$		ns
Data input hold time (from $\overline{DSTB}\uparrow$)	<16> t_{HDID}		0		ns
Address output time from $\overline{DSTB}\uparrow$	<17> t_{DDA}		$(1 + i)T - 15$		ns
Delay time from $\overline{DSTB}\uparrow$ to $ASTB\uparrow$	<18> t_{DDST1}		$0.5T - 15$		ns
Delay time from $\overline{DSTB}\uparrow$ to $ASTB\downarrow$	<19> t_{DDST2}		$(1.5 + i)T - 15$		ns
\overline{DSTB} low-level width	<20> t_{WDL}		$(1 + n)T - 22$		ns
$ASTB$ high-level width	<21> t_{WSTH}		$T - 15$		ns
Data output time from $\overline{DSTB}\downarrow$	<22> t_{DOD}			10	ns
Data output setup time (to $\overline{DSTB}\uparrow$)	<23> t_{SODD}		$(1 + n)T - 25$		ns
Data output hold time (from $\overline{DSTB}\uparrow$)	<24> t_{HDOD}		$T - 20$		ns
\overline{WAIT} setup time (to address)	<25> t_{SAWT1}	$n \geq 1$		$1.5T - 40$	ns
	<26> t_{SAWT2}	$n \geq 1$		$(1.5 + n)T - 40$	ns
\overline{WAIT} hold time (from address)	<27> t_{HAWT1}	$n \geq 1$	$(0.5 + n)T$		ns
	<28> t_{HAWT2}	$n \geq 1$	$(1.5 + n)T$		ns
\overline{WAIT} setup time (to $ASTB\downarrow$)	<29> t_{SSTWT1}	$n \geq 1$		$T - 32$	ns
	<30> t_{SSTWT2}	$n \geq 1$		$(1 + n)T - 32$	ns
\overline{WAIT} hold time (from $ASTB\downarrow$)	<31> t_{HSTWT1}	$n \geq 1$	nT		ns
	<32> t_{HSTWT2}	$n \geq 1$	$(1 + n)T$		ns
\overline{HLDRQ} high-level width	<33> t_{WHQH}		$T + 10$		ns
\overline{HLDAK} low-level width	<34> t_{WHAL}		$T - 15$		ns
Bus output delay time from $\overline{HLDAK}\uparrow$	<35> t_{DHAC}		-6		ns
Delay time from $\overline{HLDRQ}\downarrow$ to $\overline{HLDAK}\downarrow$	<36> t_{DHQA1}			$(2n + 7.5)T + 25$	ns
Delay time from $\overline{HLDRQ}\uparrow$ to $\overline{HLDAK}\uparrow$	<37> t_{DHQA2}		$0.5T$	$1.5T + 25$	ns

- Remarks**
1. $T = 1/f_{CPU}$ (f_{CPU} : CPU operating clock frequency)
 2. n : Number of wait clocks inserted in the bus cycle.
The sampling timing changes when a programmable wait is inserted.
 3. i : Number of idle states inserted after a read cycle (0 or 1).
 4. The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.

(b) Clock asynchronous ($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = 3.0$ to 4.0 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Address setup time (to $ASTB\downarrow$)	<10> t_{SAST}		$0.5T - 20$		ns
Address hold time (from $ASTB\downarrow$)	<11> t_{HSTA}		$0.5T - 20$		ns
Address float delay time from $\overline{DSTB}\downarrow$	<12> t_{FDA}			0	ns
Data input setup time from address	<13> t_{SAID}			$(2 + n)T - 50$	ns
Data input setup time from $\overline{DSTB}\downarrow$	<14> t_{SDID}			$(1 + n)T - 50$	ns
Delay time from $ASTB\downarrow$ to $\overline{DSTB}\downarrow$	<15> t_{DSTD}		$0.5T - 15$		ns
Data input hold time (from $\overline{DSTB}\uparrow$)	<16> t_{HDID}		0		ns
Address output time from $\overline{DSTB}\uparrow$	<17> t_{DDA}		$(1 + i)T - 15$		ns
Delay time from $\overline{DSTB}\uparrow$ to $ASTB\uparrow$	<18> t_{DDST1}		$0.5T - 15$		ns
Delay time from $\overline{DSTB}\uparrow$ to $ASTB\downarrow$	<19> t_{DDST2}		$(1.5 + i)T - 15$		ns
\overline{DSTB} low-level width	<20> t_{WDL}		$(1 + n)T - 35$		ns
$ASTB$ high-level width	<21> t_{WSTH}		$T - 15$		ns
Data output time from $\overline{DSTB}\downarrow$	<22> t_{DDOD}			10	ns
Data output setup time (to $\overline{DSTB}\uparrow$)	<23> t_{SODD}		$(1 + n)T - 35$		ns
Data output hold time (from $\overline{DSTB}\uparrow$)	<24> t_{HDOD}		$T - 25$		ns
\overline{WAIT} setup time (to address)	<25> t_{SAWT1}	$n \geq 1$		$1.5T - 55$	ns
	<26> t_{SAWT2}	$n \geq 1$		$(1.5 + n)T - 55$	ns
\overline{WAIT} hold time (from address)	<27> t_{HAWT1}	$n \geq 1$	$(0.5 + n)T$		ns
	<28> t_{HAWT2}	$n \geq 1$	$(1.5 + n)T$		ns
\overline{WAIT} setup time (to $ASTB\downarrow$)	<29> t_{SSWT1}	$n \geq 1$		$T - 45$	ns
	<30> t_{SSWT2}	$n \geq 1$		$(1 + n)T - 45$	ns
\overline{WAIT} hold time (from $ASTB\downarrow$)	<31> t_{HSTWT1}	$n \geq 1$	nT		ns
	<32> t_{HSTWT2}	$n \geq 1$	$(1 + n)T$		ns
\overline{HLDRQ} high-level width	<33> t_{WHQH}		$T + 10$		ns
\overline{HLDAK} low-level width	<34> t_{WHAL}		$T - 25$		ns
Bus output delay time from $\overline{HLDAK}\uparrow$	<35> t_{DHAC}		-6		ns
Delay time from $\overline{HLDRQ}\downarrow$ to $\overline{HLDAK}\downarrow$	<36> t_{DQHA1}			$(2n + 7.5)T + 25$	ns
Delay time from $\overline{HLDRQ}\uparrow$ to $\overline{HLDAK}\uparrow$	<37> t_{DQHA2}		$0.5T$	$1.5T + 25$	ns

- Remarks**
1. $T = 1/f_{CPU}$ (f_{CPU} : CPU operating clock frequency)
 2. n : Number of wait clocks inserted in the bus cycle.
The sampling timing changes when a programmable wait is inserted.
 3. i : Number of idle states inserted after a read cycle (0 or 1).
 4. The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.

(c) Clock synchronous ($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = BV_{DD} = 4.0$ to 5.5 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<38> t_{DKA}		0	19	ns
Delay time from CLKOUT↑ to address float	<39> t_{FKA}		-12	10	ns
Delay time from CLKOUT↓ to ASTB	<40> t_{DKST}		0	19	ns
Delay time from CLKOUT↑ to \overline{DSTB}	<41> t_{DKD}		0	19	ns
Data input setup time (to CLKOUT↑)	<42> t_{SIDK}		20		ns
Data input hold time (from CLKOUT↑)	<43> t_{HKID}		5		ns
Data output delay time from CLKOUT↑	<44> t_{DKOD}			19	ns
\overline{WAIT} setup time (to CLKOUT↓)	<45> t_{SWTK}		20		ns
\overline{WAIT} hold time (from CLKOUT↓)	<46> t_{HKWT}		5		ns
\overline{HLDRQ} setup time (to CLKOUT↓)	<47> t_{SHQK}		20		ns
\overline{HLDRQ} hold time (from CLKOUT↓)	<48> t_{HKHQ}		5		ns
Delay time from CLKOUT↑ to address float (during bus hold)	<49> t_{DKF}			19	ns
Delay time from CLKOUT↑ to \overline{HLDAK}	<50> t_{DKHA}			19	ns

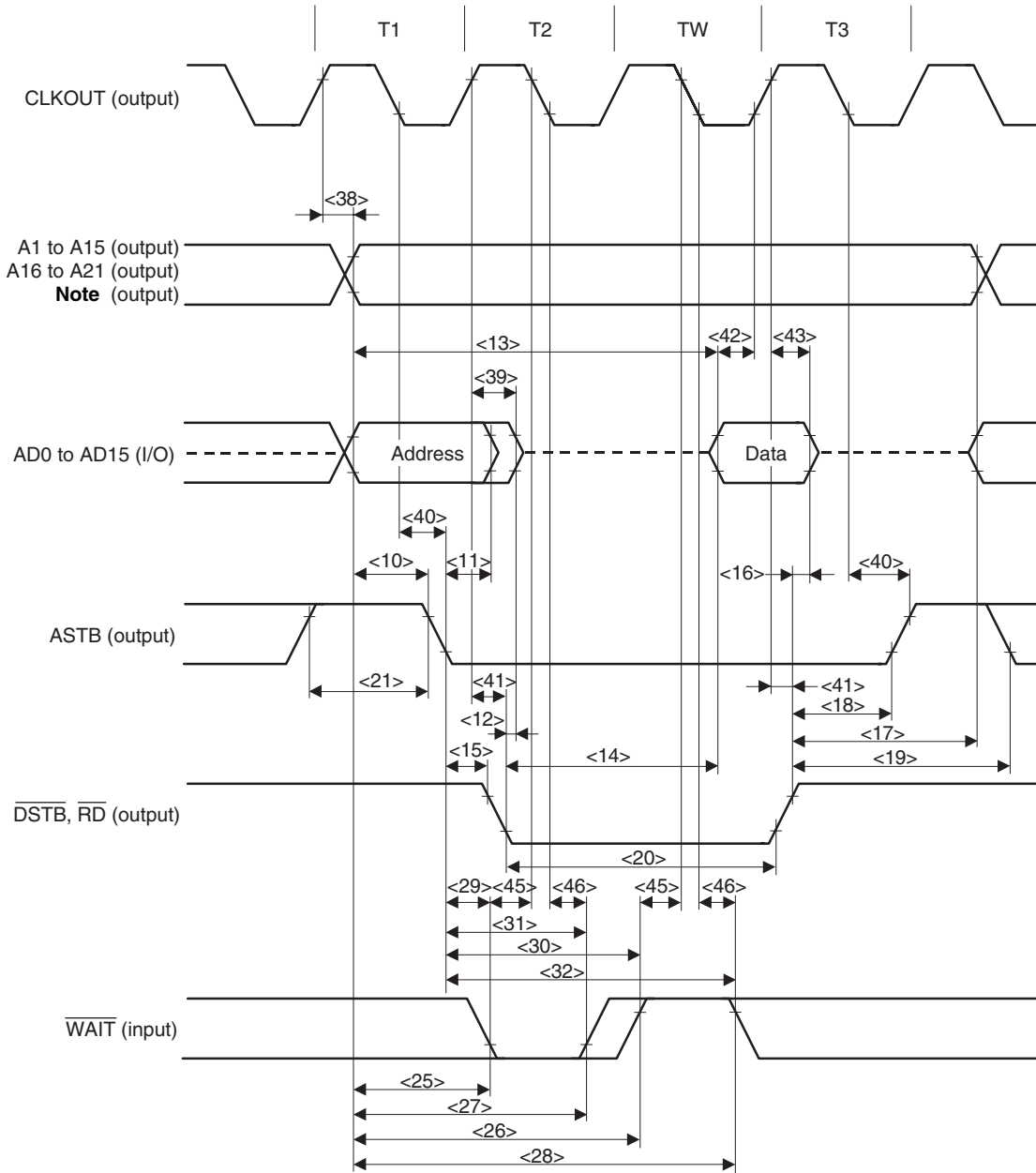
Remark The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.

(d) Clock synchronous ($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = 3.0$ to 4.0 V, $EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
Delay time from CLKOUT↑ to address	<38> t_{DKA}		0	22	ns
Delay time from CLKOUT↑ to address float	<39> t_{FKA}		-16	10	ns
Delay time from CLKOUT↓ to ASTB	<40> t_{DKST}		0	19	ns
Delay time from CLKOUT↑ to \overline{DSTB}	<41> t_{DKD}		0	22	ns
Data input setup time (to CLKOUT↑)	<42> t_{SIDK}		20		ns
Data input hold time (from CLKOUT↑)	<43> t_{HKID}		5		ns
Data output delay time from CLKOUT↑	<44> t_{DKOD}			22	ns
\overline{WAIT} setup time (to CLKOUT↓)	<45> t_{SWTK}		24		ns
\overline{WAIT} hold time (from CLKOUT↓)	<46> t_{HKWT}		5		ns
\overline{HLDRQ} setup time (to CLKOUT↓)	<47> t_{SHQK}		24		ns
\overline{HLDRQ} hold time (from CLKOUT↓)	<48> t_{HKHQ}		5		ns
Delay time from CLKOUT↑ to address float (during bus hold)	<49> t_{DKF}			19	ns
Delay time from CLKOUT↑ to \overline{HLDAK}	<50> t_{DKHA}			19	ns

Remark The values in the above specifications are values for when clocks with a 5:5 duty ratio are input from X1.

(e) Read cycle (CLKOUT synchronous/asynchronous, 1 wait)

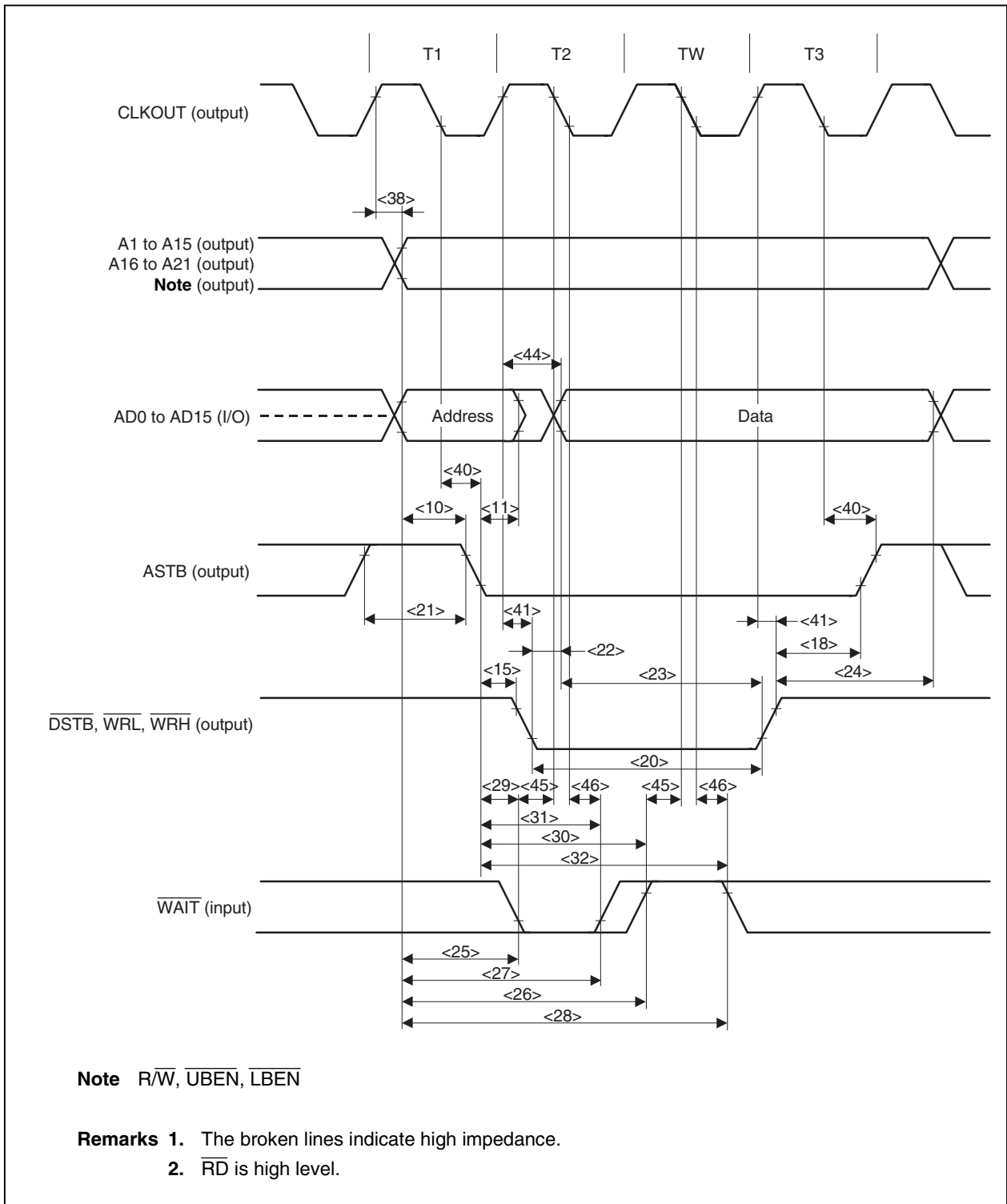


Note $\overline{R/W}$, \overline{UBEN} , \overline{LBEN}

- Remarks 1. The broken lines indicate high impedance.
 2. \overline{WRL} and \overline{WRH} are high level.

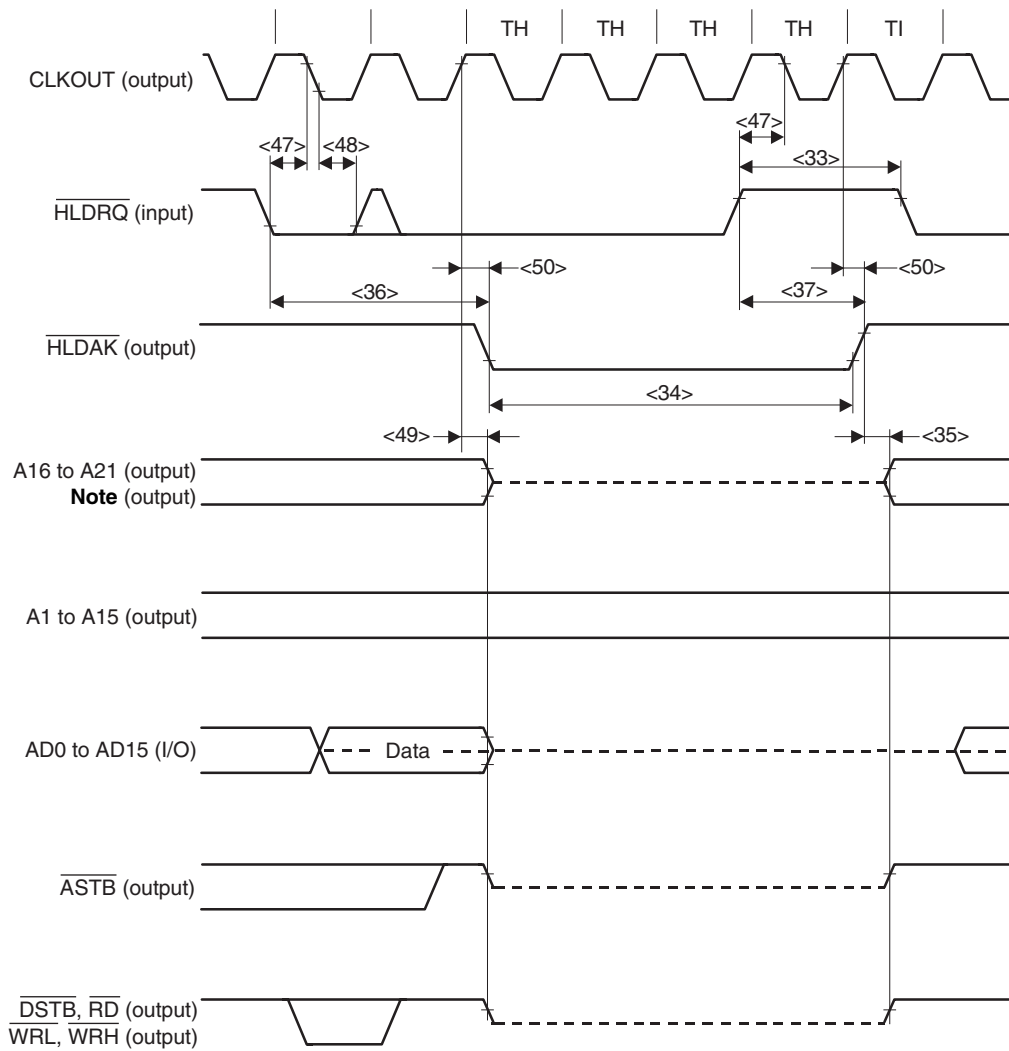
★

(f) Write cycle (CLKOUT synchronous/asynchronous, 1 wait)



★

(g) Bus hold timing



Note $\overline{R/W}$, \overline{UBEN} , \overline{LBEN}

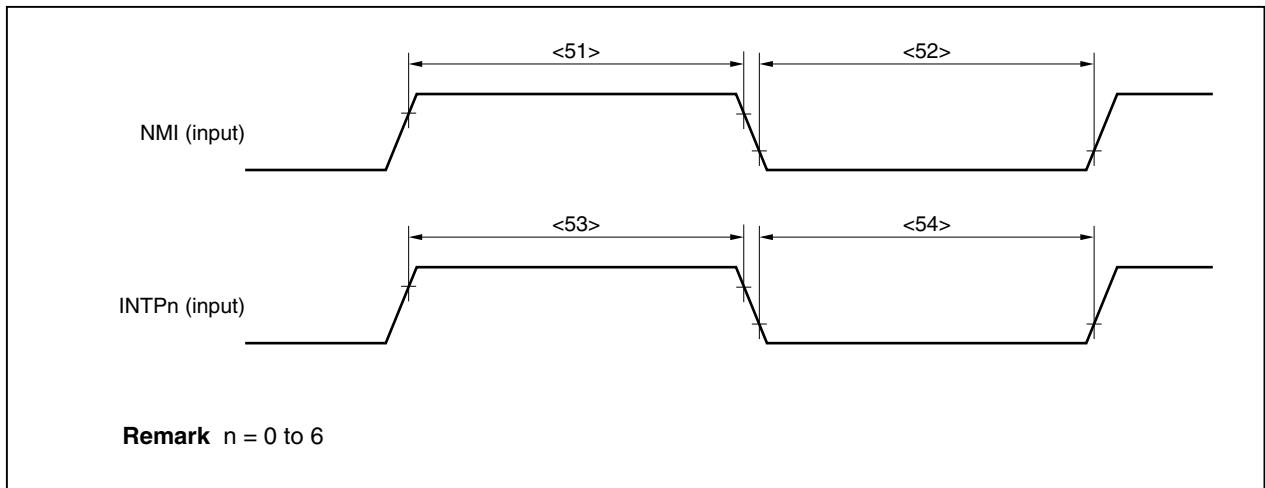
Remark The broken lines indicate high impedance.

(5) Interrupt timing

(T_A = -40 to +85°C, V_{DD} = 4.0 to 5.5 V, BV_{DD} = EV_{DD} = 3.0 to 5.5 V, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
NMI high-level width	<51> t _{WNH}		500		ns
NMI low-level width	<52> t _{WNL}		500		ns
INTPn high-level width	<53> t _{WITH}	n = 0 to 3, analog noise elimination	500		ns
		n = 4, 5, digital noise elimination	3T + 20		ns
		n = 6, digital noise elimination	3T _{smp} + 20		ns
INTPn low-level width	<54> t _{WTL}	n = 0 to 3, analog noise elimination	500		ns
		n = 4, 5, digital noise elimination	3T + 20		ns
		n = 6, digital noise elimination	3T _{smp} + 20		ns

- Remarks**
1. T = 1/f_{xx}
 2. T_{smp} = Noise elimination sampling clock cycle



(6) RPU timing

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
TIn0, TIn1 high-level width	<55> t_{rIHn}	$n = 0, 1$	$2T_{sam} + 20^{Note}$		ns
TIn0, TIn1 low-level width	<56> t_{rILn}	$n = 0, 1$	$2T_{sam} + 20^{Note}$		ns
TIm high-level width	<57> t_{rIHm}	$m = 2$ to 5	$3T + 20$		ns
TIm low-level width	<58> t_{rILm}	$m = 2$ to 5	$3T + 20$		ns

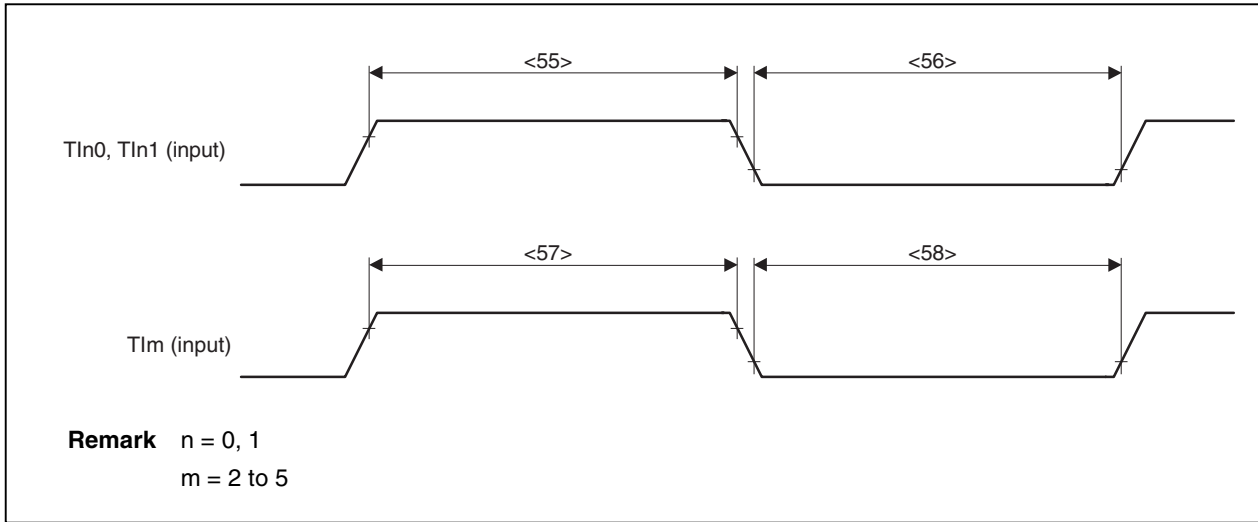
Note T_{sam} can select the following count clocks by setting the PRMn2 to PRMn0 bits of prescaler mode registers n0, n1 (PRMn0, PRMn1).

When $n = 0$ (TM0), $T_{sam} = 2T, 4T, 16T, 64T, 256T$, or $1/INTWNTNI$ cycle

When $n = 1$ (TM1), $T_{sam} = 2T, 4T, 16T, 32T, 128T$, or $256T$

However, when the TIn0 valid edge is selected as the count clock, $T_{sam} = 4T$.

Remark $T = 1/f_{xx}$

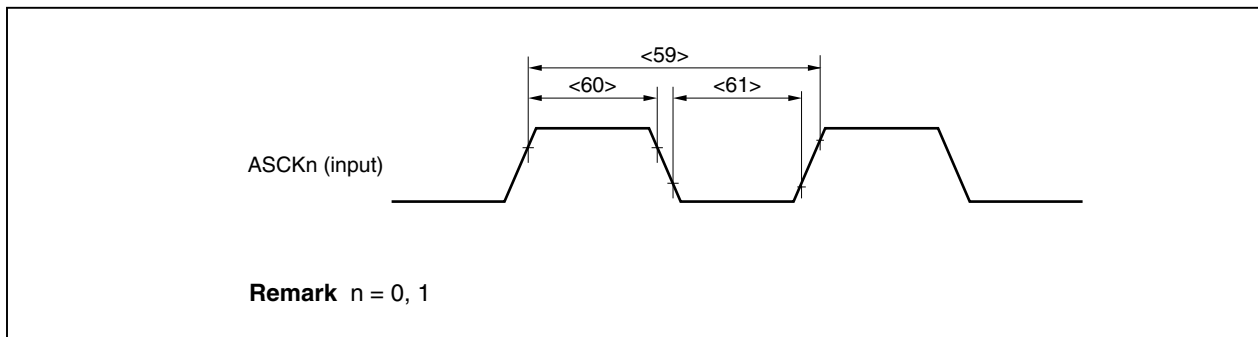


(7) Asynchronous serial interface (UART0, UART1) timing

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
ASCKn cycle time	<59> t_{kCY13}		200		ns
ASCKn high-level width	<60> t_{kH13}		80		ns
ASCKn low-level width	<61> t_{kL13}		80		ns

Remark $n = 0, 1$



(8) 3-wire serial interface (CSI0 to CSI3) timing

(a) Master mode

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
$\overline{\text{SCKn}}$ cycle	<62> t_{KCY1}		400		ns
$\overline{\text{SCKn}}$ high-level width	<63> t_{KH1}		140		ns
$\overline{\text{SCKn}}$ low-level width	<64> t_{KL1}		140		ns
SIn setup time (to $\overline{\text{SCKn}}\uparrow$)	<65> t_{SIK1}		50		ns
SIn hold time (from $\overline{\text{SCKn}}\uparrow$)	<66> t_{KSI1}		50		ns
Delay time from $\overline{\text{SCKn}}\downarrow$ to SOn output	<67> t_{KSO1}			60	ns

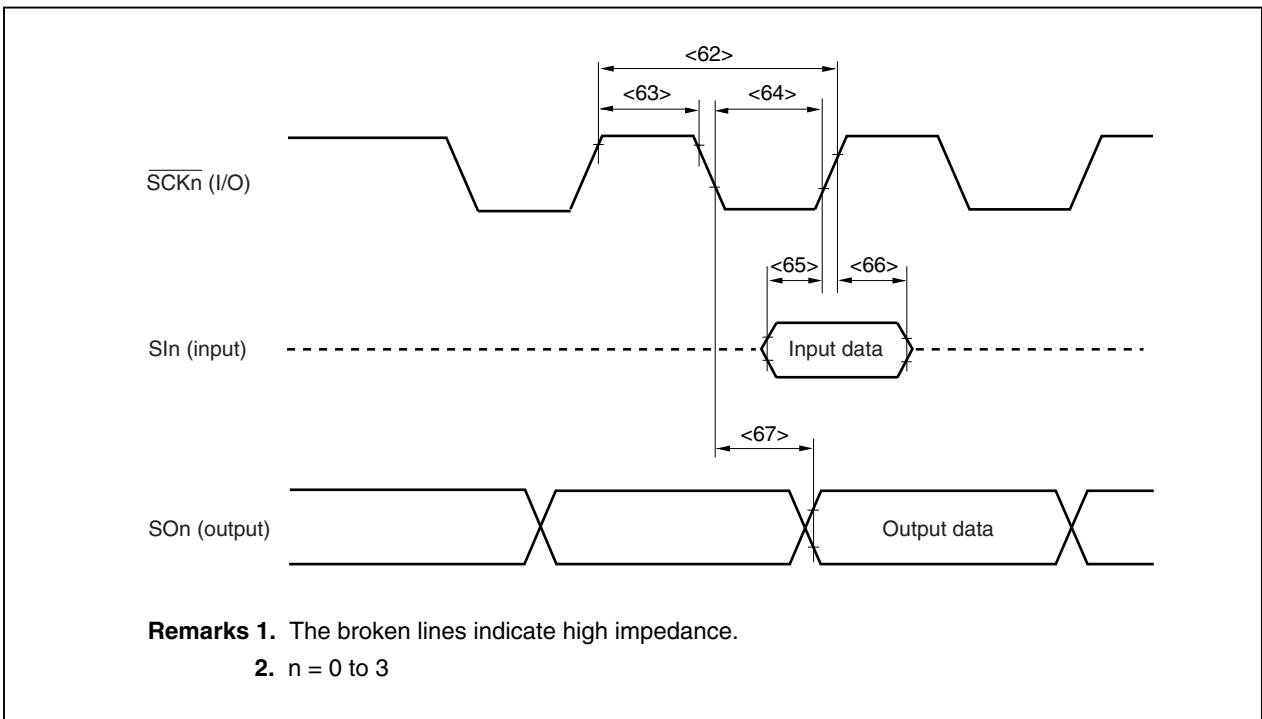
Remark n = 0 to 3

(b) Slave mode

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = V_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
$\overline{\text{SCKn}}$ cycle	<62> t_{KCY2}		400		ns
$\overline{\text{SCKn}}$ high-level width	<63> t_{KH2}		140		ns
$\overline{\text{SCKn}}$ low-level width	<64> t_{KL2}		140		ns
SIn setup time (to $\overline{\text{SCKn}}\uparrow$)	<65> t_{SIK2}		50		ns
SIn hold time (from $\overline{\text{SCKn}}\uparrow$)	<66> t_{KSI2}		50		ns
Delay time from $\overline{\text{SCKn}}\downarrow$ to SOn output	<67> t_{KSO2}	$4.0\text{ V} \leq EV_{DD} \leq 5.5\text{ V}$		60	ns
		$3.0\text{ V} \leq EV_{DD} < 4.0\text{ V}$		100	ns

Remark n = 0 to 3



(9) 3-wire variable length serial interface (CSI4) timing

(a) Master mode

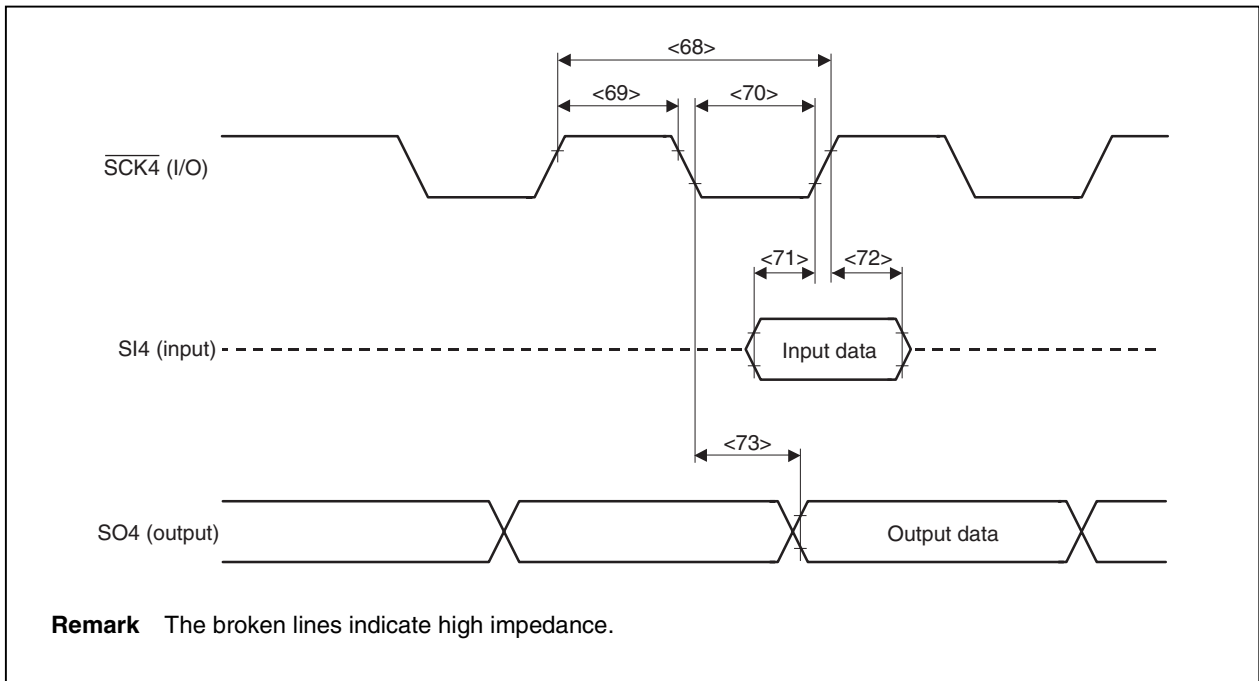
($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit	
$\overline{\text{SCK4}}$ cycle	<68>	t_{KCY1}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	200		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	400		ns
$\overline{\text{SCK4}}$ high-level width	<69>	t_{KH1}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	60		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	140		ns
$\overline{\text{SCK4}}$ low-level width	<70>	t_{KL1}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	60		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	140		ns
SI4 setup time (to $\overline{\text{SCK4}}\uparrow$)	<71>	t_{SIK1}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	25		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	50		ns
SI4 hold time (from $\overline{\text{SCK4}}\uparrow$)	<72>	t_{KS1}	20		ns	
Delay time from $\overline{\text{SCK4}}\downarrow$ to SO4 output	<73>	t_{KS01}		55	ns	

(b) Slave mode

($T_A = -40$ to $+85^\circ\text{C}$, $V_{DD} = 4.0$ to 5.5 V, $BV_{DD} = EV_{DD} = 3.0$ to 5.5 V, $V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0$ V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit	
$\overline{\text{SCK4}}$ cycle	<68>	t_{KCY2}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	200		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	400		ns
$\overline{\text{SCK4}}$ high-level width	<69>	t_{KH2}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	60		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	140		ns
$\overline{\text{SCK4}}$ low-level width	<70>	t_{KL2}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	60		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	140		ns
SI4 setup time (to $\overline{\text{SCK4}}\uparrow$)	<71>	t_{SIK2}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$	25		ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$	50		ns
SI4 hold time (from $\overline{\text{SCK4}}\uparrow$)	<72>	t_{KS2}	20		ns	
Delay time from $\overline{\text{SCK4}}\downarrow$ to SO4 output	<73>	t_{KS02}	$4.0 \text{ V} \leq EV_{DD} \leq 5.5 \text{ V}$		55	ns
			$3.0 \text{ V} \leq EV_{DD} < 4.0 \text{ V}$		100	ns



(10) I²C bus mode (μPD703034AY, 703035AY, 70F3035AY only) (1/2)

(T_A = -40 to +85°C, V_{DD} = 4.0 to 5.5 V, BV_{DD} = EV_{DD} = 3.0 to 5.5 V, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V)

Parameter		Symbol	Normal Mode		High-Speed Mode		Unit	
			MIN.	MAX.	MIN.	MAX.		
SCLn clock frequency		-	f _{CLK}	0	100	0	400	kHz
Bus-free time (between stop/start conditions)		<74>	t _{BUF}	4.7	-	1.3	-	μs
Hold time ^{Note 1}		<75>	t _{HD:STA}	4.0	-	0.6	-	μs
SCLn clock low-level width		<76>	t _{LOW}	4.7	-	1.3	-	μs
SCLn clock high-level width		<77>	t _{HIGH}	4.0	-	0.6	-	μs
Setup time for start/restart conditions		<78>	t _{SU:STA}	4.7	-	0.6	-	μs
Data hold time	CBUS compatible master	<79>	t _{HD:DAT}	5.0	-	-	-	μs
	I ² C mode			0 ^{Note 2}	-	0 ^{Note 2}	0.9 ^{Note 3}	μs
Data setup time		<80>	t _{SU:DAT}	250	-	100 ^{Note 4}	-	ns
SDAn and SCLn signal rise time		<81>	t _R	-	1000	20 + 0.1Cb ^{Note 5}	300	ns
SDAn and SCLn signal fall time		<82>	t _F	-	300	20 + 0.1Cb ^{Note 5}	300	ns
Stop condition setup time		<83>	t _{SU:STO}	4.0	-	0.6	-	μs
Pulse width of spike suppressed by input filter		<84>	t _{SP}	-	-	0	50	ns
Capacitance load of each bus line		-	C _b	-	400	-	400	pF

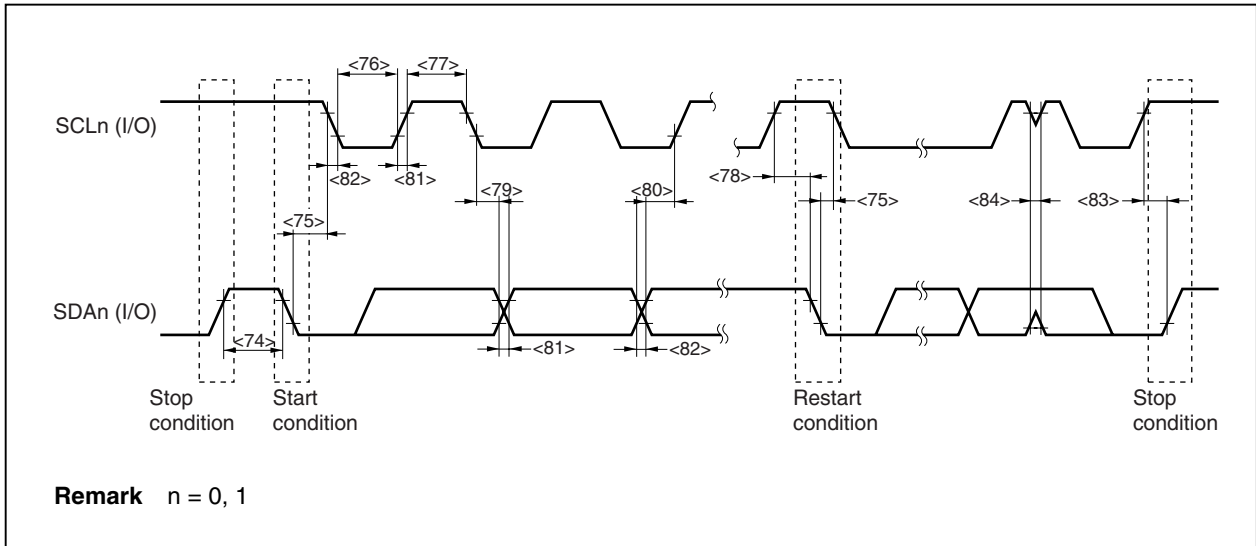
- Notes**
- At the start condition, the first clock pulse is generated after the hold time.
 - The system requires a minimum of 300 ns hold time internally for the SDAn signal (at V_{IHmin.} of SCLn signal) in order to occupy the undefined area at the falling edge of SCLn.
 - If the system does not extend the SCLn signal low hold time (t_{LOW}), only the maximum data hold time (t_{HD:DAT}) needs to be satisfied.
 - The high-speed mode I²C bus can be used in the normal-mode I²C bus system. In this case, set the high-speed mode I²C bus so that it meets the following conditions.
 - If the system does not extend the SCLn signal's low state hold time:

$$t_{SU:DAT} \geq 250 \text{ ns}$$
 - If the system extends the SCLn signal's low state hold time:

Transmit the following data bit to the SDAn line prior to the SCLn line release (t_{Rmax.} + t_{SU:DAT} = 1000 + 250 = 1250 ns: Normal mode I²C bus specification).
 - C_b: Total capacitance of one bus line (unit: pF)

Remark n = 0, 1

(10) I²C bus mode (μPD703034AY, 703035AY, 70F3035AY only) (2/2)



A/D Converter Characteristics (T_A = -40 to +85°C, V_{DD} = AV_{DD} = AV_{REF} = 4.5 to 5.5 V, V_{SS} = AV_{SS} = 0 V, Output pin load capacitance: C_L = 50 pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Resolution	—		10	10	10	bit	
Overall error ^{Note 1}	—	ADM2 = 00H			±0.6	%FSR	
		ADM2 = 01H			±1.0	%FSR	
Conversion time	t _{CONV}		5		10	μs	
Zero-scale error ^{Note 1}					±0.4	%FSR	
Full-scale error ^{Note 1}		ADM2 = 00H			±0.4	%FSR	
		ADM2 = 01H			±0.6	%FSR	
Integral linearity error ^{Note 2}		ADM2 = 00H			±4.0	LSB	
		ADM2 = 01H			±6.0	LSB	
Differential linearity error ^{Note 2}		ADM2 = 00H			±4.0	LSB	
		ADM2 = 01H			±6.0	LSB	
Analog reference voltage	AV _{REF}	AV _{REF} = AV _{DD}	4.5		5.5	V	
Analog power supply voltage	AV _{DD}		4.5		5.5	V	
Analog input voltage	V _{IAN}		AV _{SS}		AV _{REF}	V	
AV _{REF} input current	AI _{REF}			1	2	mA	
AV _{DD} power supply current	AI _{DD}	Operating current	ADM2 = 00H		3	6	mA
			ADM2 = 01H		4	8	mA

- Notes** 1. Excluding quantization error (±0.05 %FSR)
 2. Excluding quantization error (±0.5 LSB)

- Remarks** 1. LSB: Least Significant Bit
 FSR: Full Scale Range
 2. ADM2: A/D converter mode register 2

IEBus Controller Characteristics (T_A = -40 to +85°C, V_{DD} = 4.0 to 5.5 V, BV_{DD} = EV_{DD} = 3.0 to 5.5 V, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
IEBus system clock frequency	f _s	Communication mode: fixed to mode 1		6.0 ^{Note 1}		MHz
				6.29 ^{Notes 1, 2}		MHz

- Notes**
- 6.0 MHz and 6.29 MHz can not be used together for the IEBus system clock frequency
 - Although the system clock specified in the IEBus specification is 6.0 MHz, operation is guaranteed at 6.29 MHz system clock in the V850/SB2.

Regulator (T_A = -40 to +85°C, V_{DD} = 4.0 to 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output stabilization time	t _{REG}	Stabilization capacitance C = 1 μF (Connected to REGC pin)	1			ms

- Cautions**
- Be sure to start inputting supply voltage V_{DD} when $\overline{\text{RESET}} = V_{SS} = EV_{SS} = BV_{SS} = 0 \text{ V}$ (the above state), and make $\overline{\text{RESET}}$ high level after the t_{REG} period has elapsed.
 - If supply voltage BV_{DD} or EV_{DD} is input before the t_{REG} period has elapsed following the input of supply voltage V_{DD}, note that data may be driven from the pins until the t_{REG} period has elapsed because the I/O buffers' power supply was turned on while the circuit was in an undefined state.

★ 3.1 Flash Memory Programming Mode (μPD70F3035A, 70F3035AY only)

Write/erase characteristics (T_A = 10 to 85°C ... I, K, E rank product,
 T_A = -20 to +85°C ... P rank product,
 V_{DD} = AV_{DD} = BV_{DD} = EV_{DD} = 4.5 to 5.5 V, V_{SS} = AV_{SS} = BV_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V _{PP} power supply voltage	V _{PP2}	During flash memory programming	7.5	7.8	8.1	V
V _{DD} power supply current	I _{DD}	When V _{PP} = V _{PP2} , f _{XX} = 13 MHz			51	mA
V _{PP} power supply current	I _{PP}	V _{PP} = V _{PP2}			100	mA
Step erase time	t _{ER}	Note 1		0.2		s
Overall erase time per area	t _{ERA}	When the step erase time = 0.2 s, Note 2			20	s/area
Write-back time	t _{WB}	Note 3		1		ms
Number of write-backs per write-back command	C _{WB}	When the write-back time = 1 ms, Note 4			300	Count/write-back command
Number of erase/write-backs	C _{ERWB}				16	Count
Step writing time	t _{WR}	Note 5		20		μs
Overall writing time per word	t _{WRW}	When the step writing time = 20 μs (1 word = 4 bytes), Note 6	20		200	μs/word
Number of rewrites per area	C _{ERWR}	1 erase + 1 write after erase = 1 rewrite, Note 7	Note 8			Count/area

- Notes 1.** The recommended setting value of the step erase time is 0.2 s.
2. The prewrite time prior to erasure and the erase verify time (write-back time) are not included.
3. The recommended setting value of the write-back time is 1 ms.
4. Write-back is executed once by the issuance of the write-back command. Therefore, the retry count must be the maximum value minus the number of commands issued.
5. The recommended setting value of the step writing time is 20 μs.
6. 20 μs is added to the actual writing time per word. The internal verify time during and after the writing is not included.
7. When writing initially to shipped products, it is counted as one rewrite for both “erase to write” and “write only”.

Example (P: Write, E: Erase)

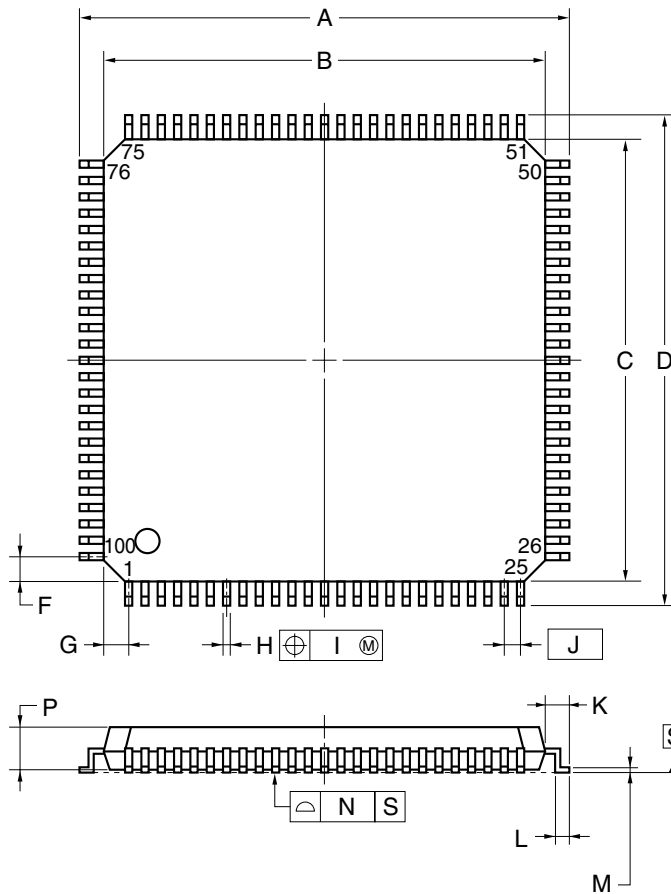
Shipped product → P → E → P → E → P: 3 rewrites
 Shipped product → E → P → E → P → E → P: 3 rewrites

- 8.** I, K, E rank product: 20 writes/area
 P rank product: 100 writes/area

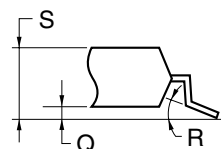
- Remarks 1.** When the PG-FP3 is used, a time parameter required for writing/erasing by downloading parameter files is automatically set. Do not change the settings unless otherwise specified.
2. Area 0 = 000000H to 01FFFFH
 Area 1 = 020000H to 03FFFFH

4. PACKAGE DRAWINGS

★ 100-PIN PLASTIC LQFP (FINE PITCH) (14x14)



detail of lead end



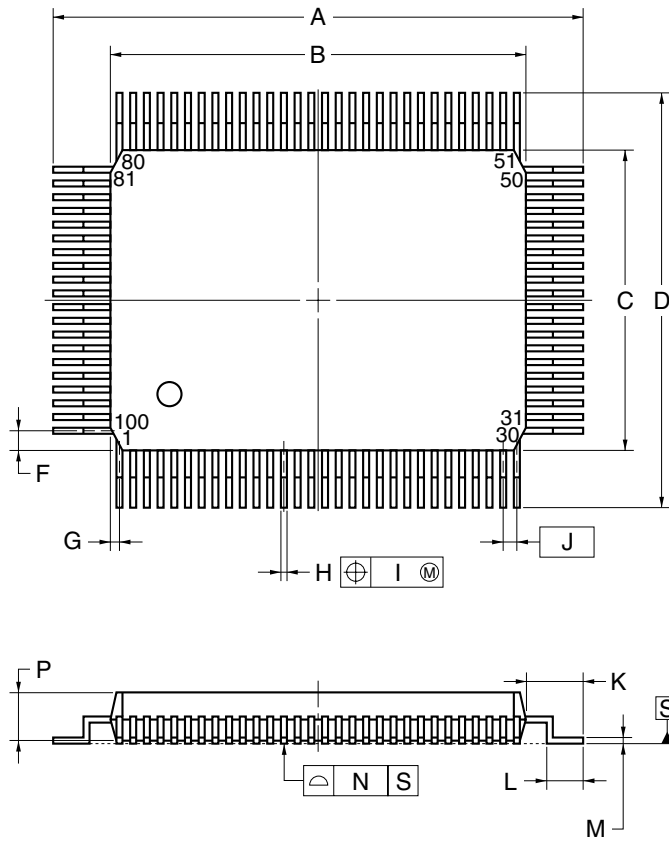
NOTE

Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	16.00±0.20
B	14.00±0.20
C	14.00±0.20
D	16.00±0.20
F	1.00
G	1.00
H	0.22 ^{+0.05} _{-0.04}
I	0.08
J	0.50 (T.P.)
K	1.00±0.20
L	0.50±0.20
M	0.17 ^{+0.03} _{-0.07}
N	0.08
P	1.40±0.05
Q	0.10±0.05
R	3° ^{+7°} _{-3°}
S	1.60 MAX.

S100GC-50-8EU, 8EA-2

100-PIN PLASTIC QFP (14x20)



detail of lead end

NOTE

Each lead centerline is located within 0.15 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	23.6±0.4
B	20.0±0.2
C	14.0±0.2
D	17.6±0.4
F	0.8
G	0.6
H	0.30±0.10
I	0.15
J	0.65 (T.P.)
K	1.8±0.2
L	0.8±0.2
M	0.15 ^{+0.10} _{-0.05}
N	0.10
P	2.7±0.1
Q	0.1±0.1
R	5°±5°
S	3.0 MAX.

P100GF-65-3BA1-4

5. RECOMMENDED SOLDERING CONDITIONS

The μPD703034A, 703034AY, 703035A, 703035AY, 70F3035A, and 70F3035AY should be soldered and mounted under the following recommended conditions.

For the details of the recommended soldering conditions, refer to the document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Table 5-1. Surface Mounting Type Soldering Conditions (1/2)

- (1) μPD703034AGC-xxx-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD703034AYGC-xxx-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD703035AGC-xxx-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD703035AYGC-xxx-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	IR35-107-2
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Two times or less Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	VP15-107-2
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	—

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

- (2) μPD70F3035AGC-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)
- μPD70F3035AYGC-8EU: 100-pin plastic LQFP (fine pitch) (14 × 14)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less Exposure limit: 3 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	IR35-103-2
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Two times or less Exposure limit: 3 days ^{Note} (after that, prebake at 125°C for 10 to 72 hours)	VP15-103-2
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	—

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

Table 5-1. Surface Mounting Type Soldering Conditions (2/2)

- (3) μPD703034AGF-xxx-3BA: 100-pin plastic QFP (14 × 20)
- μPD703034AYGF-xxx-3BA: 100-pin plastic QFP (14 × 20)
- μPD703035AGF-xxx-3BA: 100-pin plastic QFP (14 × 20)
- μPD703035AYGF-xxx-3BA: 100-pin plastic QFP (14 × 20)
- μPD70F3035AGF-3BA: 100-pin plastic QFP (14 × 20)
- μPD70F3035AYGF-3BA: 100-pin plastic QFP (14 × 20)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher), Count: Two times or less Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 20 to 72 hours)	IR35-207-2
VPS	Package peak temperature: 215°C, Time: 25 to 40 seconds (at 200°C or higher), Count: Two times or less Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 20 to 72 hours)	VP15-207-2
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once Preheating temperature: 120°C max. (package surface temperature) Exposure limit: 7 days ^{Note} (after that, prebake at 125°C for 20 to 72 hours)	WS60-207-1
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	—

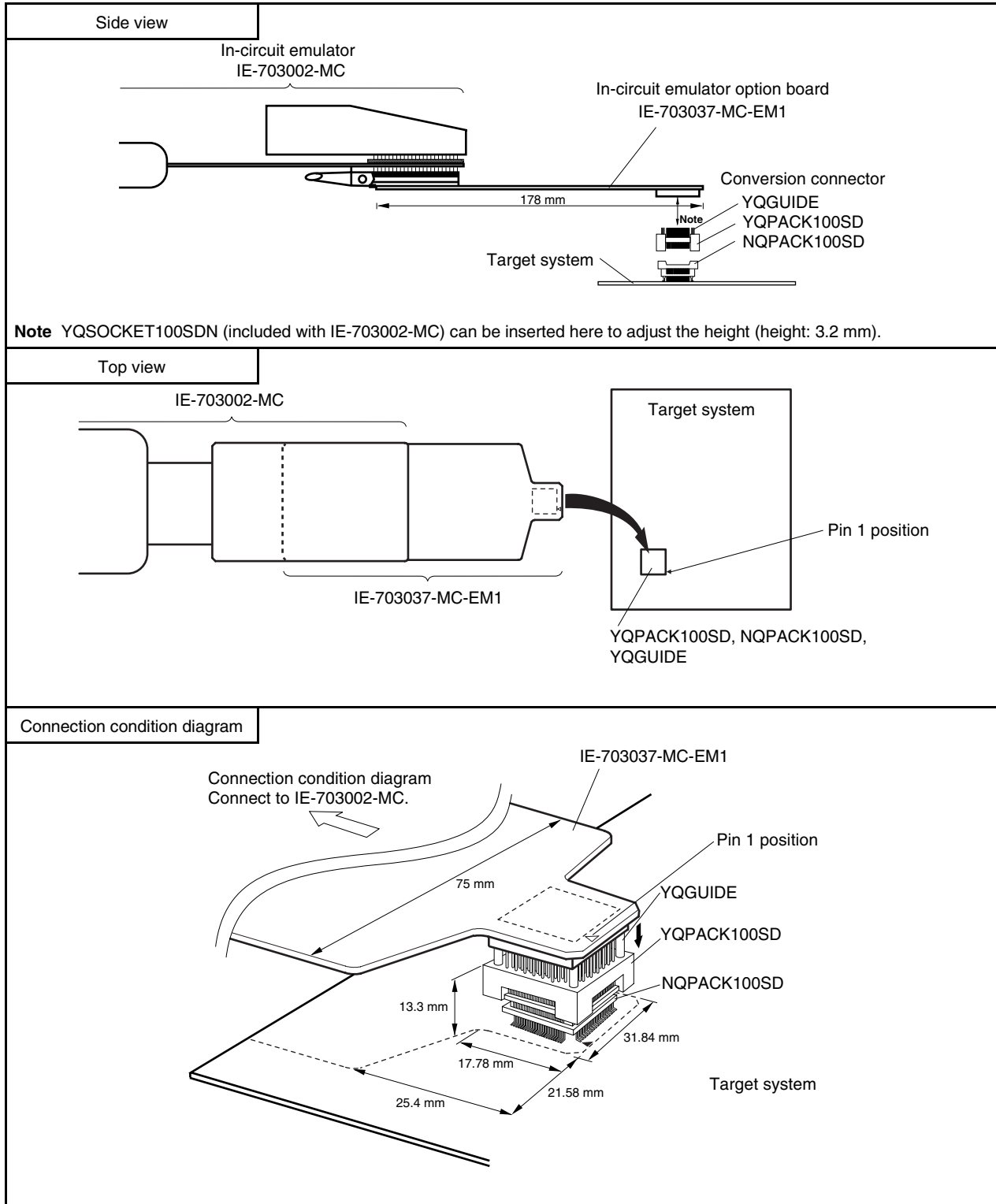
Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

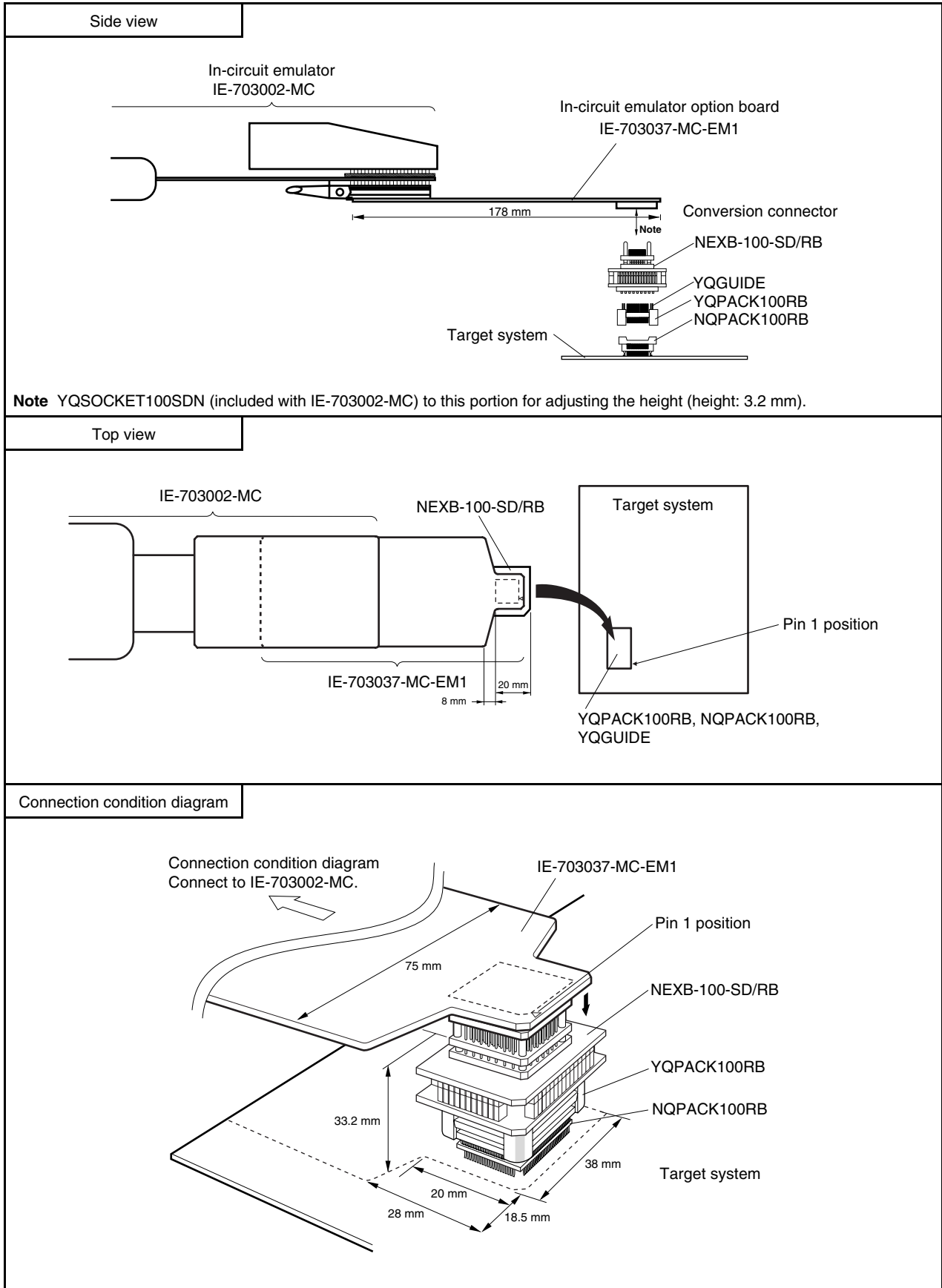
★APPENDIX NOTES ON TARGET SYSTEM DESIGN

The following shows a diagram of the connection conditions between the in-circuit emulator option board and conversion connector. Design your system making allowances for conditions such as the form of parts mounted on the target system as shown below.

Appendix-1. 100-pin Plastic LQFP (Fine Pitch) (14 × 14)



Appendix-2. 100-pin Plastic QFP (14 × 20)



NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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Related document μ PD703037A, 703037AY, 70F3037A, 70F3037AY Data Sheet (U14894E)

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Santa Clara, California
Tel: 408-588-6000
800-366-9782
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Fax: 0211-65 03 490

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Hong Kong
Tel: 2886-9318
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Seoul Branch
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Tel: 02-2719-2377
Fax: 02-2719-5951

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